



**BROOKHAVEN**  
NATIONAL LABORATORY



筑波大学  
*University of Tsukuba*



# Development an AC-LGAD sensor with fine time and spatial resolutions

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KEK, U.Tsukuba<sup>A</sup>*

# Motivation

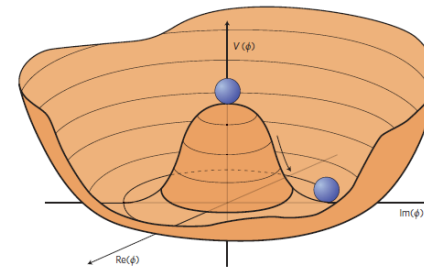
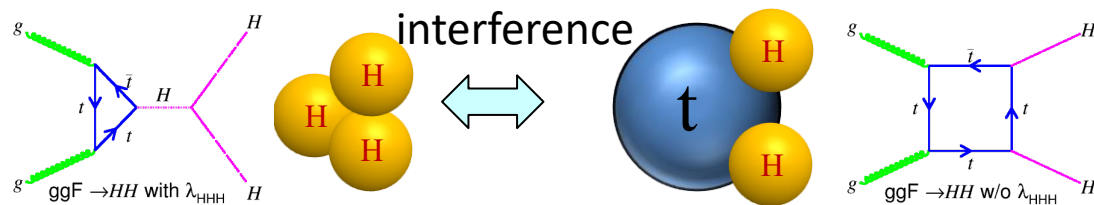
## Higgs discovery and measurement by LHC experiment



New era!

### • “Vacuum”

- “Vacuum” is nothing? Filled by Higgs boson?
- How Higgs boson/field condensed to the “Vacuum”?
- Need to determine/observe the shape of Higgs Potential.  
→ Observe/measure “Higgs self coupling”.



### • “Dark Matter/Energy”

- We only know 4%. What’s the others?
- Beyond the Standard Model?



# Next generation of Collider experiment

## Need "Higher Luminosity" and/or "Higher Energy"

### High Luminosity LHC (HL-LHC)

- 20 times more data ( $\sim 3000-4000\text{fb}^{-1}$ ) at **14TeV**
- Plan : Start at 2027

### High Energy LHC (HE-LHC)

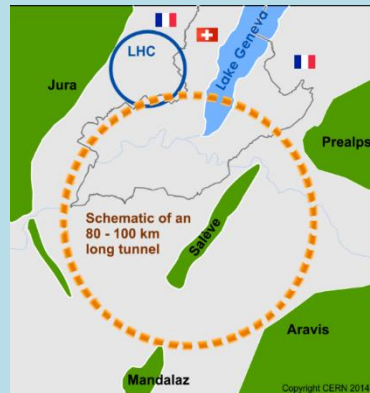
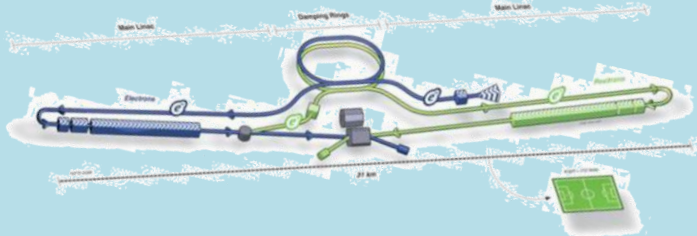
- Use Super Conducting Magnet with Higher Magnetic field(16T)
- **28TeV** collider in the same tunnel as LHC.

### Future Circular Collider (FCC-hh)

- Use Super Conducting Magnet with Higher Magnetic field(16T)
- **100TeV** collider with 100km tunnel at CERN.

### International Linear Collider (ILC)

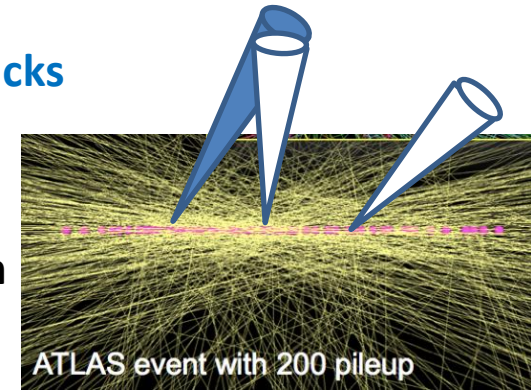
- 250GeV  $e^+ e^-$  collider in Japan



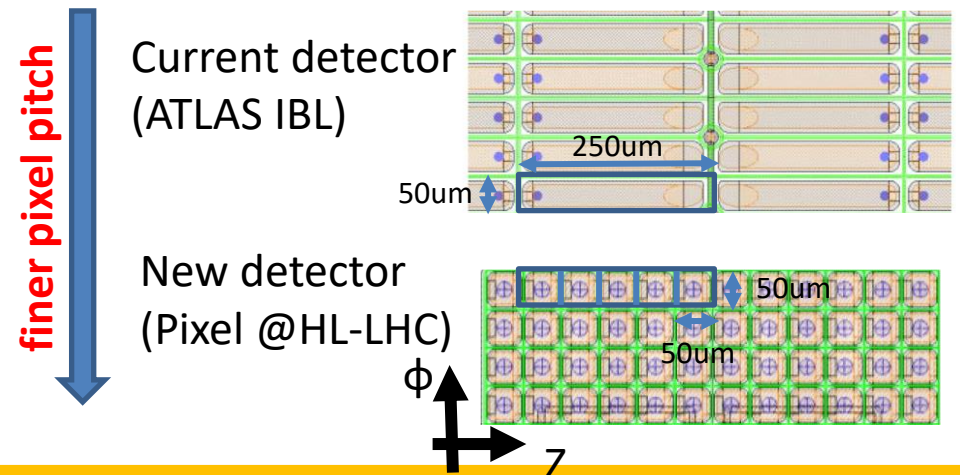
## Inner Tracking system

Very high density tracks

140 pileup @ HL-LHC  
1500 pileup @ FCC-hh



Only way to solve this so far...



Coming soon

Discussion Started

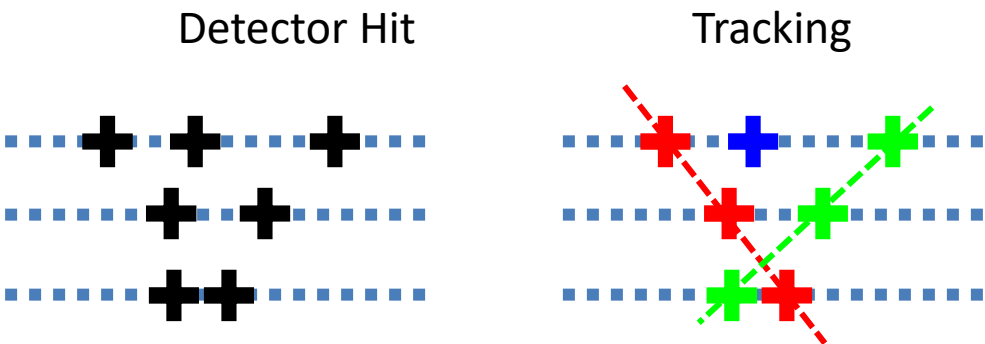
Discussion Started

Final decision soon

# Future Semi-conductor Tracking Detectors

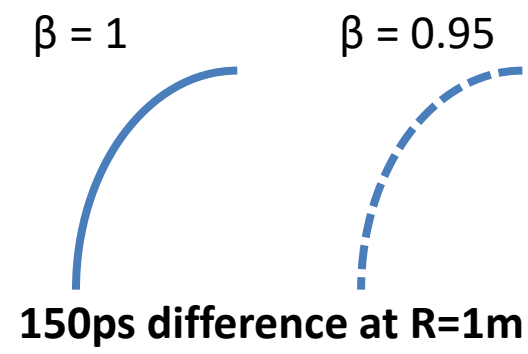
- Further finer pitch pixel detector → Limited by front end Electronics (min : 50x50um<sup>2</sup>)
  - In addition to spatial resolution, **Timing resolution helps!**
  - New generation of Tracking detector should have timing information for all hits!
- Tentative Requirement
  - **30ps timing resolution**
  - **~o(10)um spatial resolution (Pixel type).**
  - (hadron collider) ~o(10<sup>16</sup>)n<sub>eq</sub>/cm<sup>2</sup> radiation tolerance

## 4D tracking !



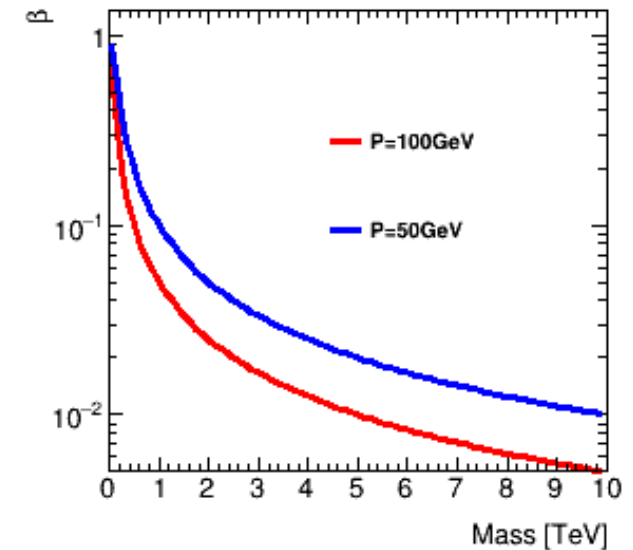
Solve pileup hits in an event

## Particle identification



K+ pi+ separation

## Mass spectrum for new particle

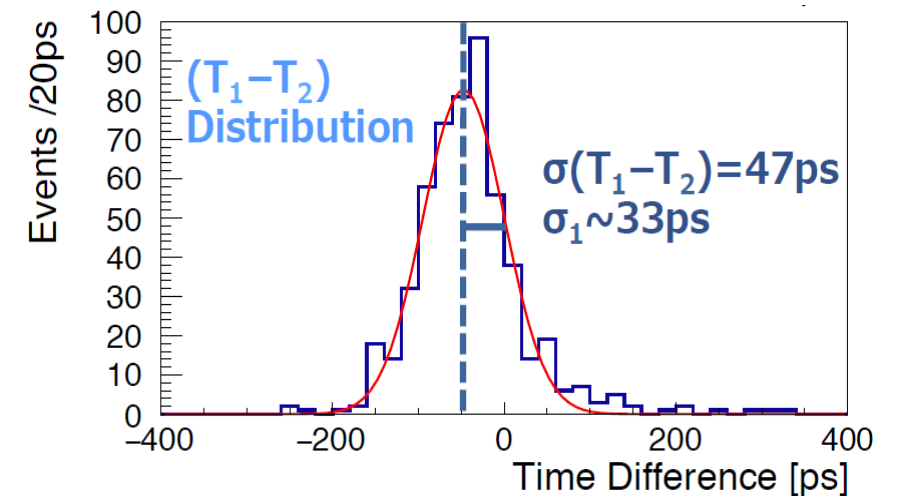
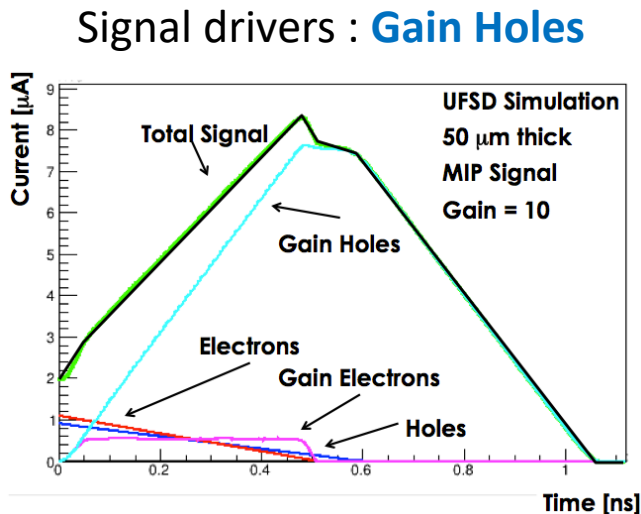
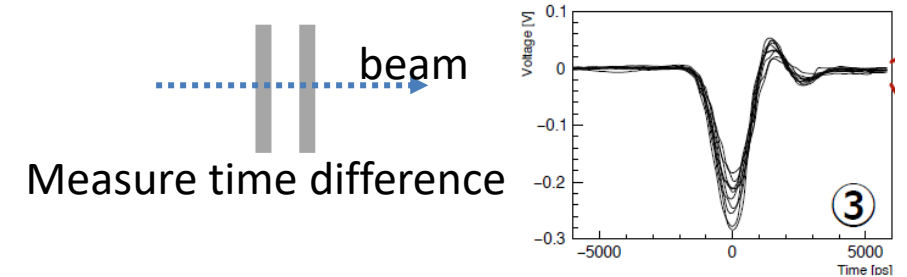
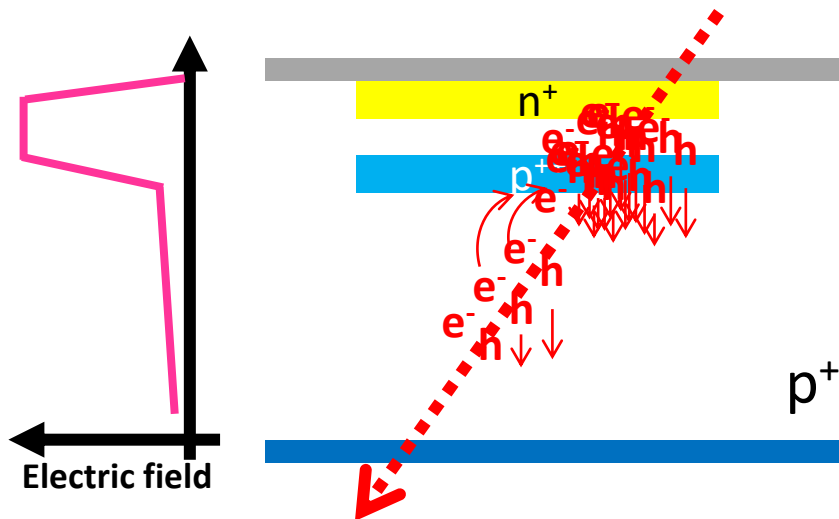


beta measurement to obtain mass

e.g. Mass measurement for Long lived chargino

# Low gain Avalanche Diode (LGAD)

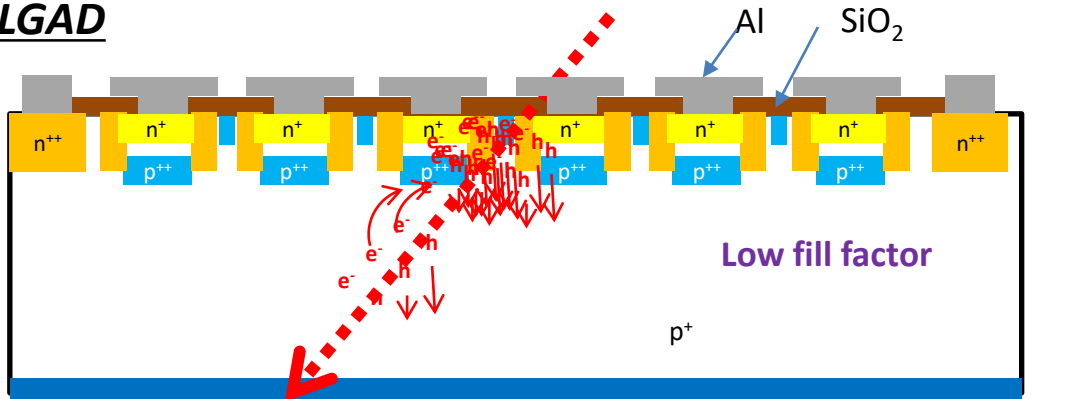
- Low gain Avalanche Diode (LGAD)
  - General  $n^+$ -in- $p$  type sensor with  $p^+$  gain layer under  $n^+$  implant to make higher Electric Field  $\rightarrow$  Good timing resolution.
  - **30ps timing resolution achieved already.**
  - Next development
    - **Finer electrode separation for spatial resolution**
    - **Radiation tolerance**



# Detector with both spatial and timing resolution

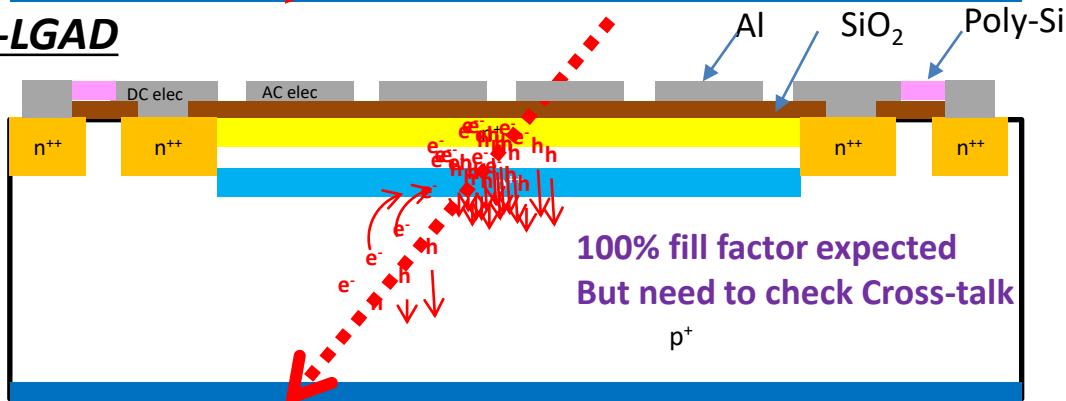
- First prototype with 80um pitch strip (DC-LGAD) → **Only 20% of active area has gain**
- Common gain layer with AC-coupled readout (AC-LGAD) → **Uniform gain expected!**
  - **Cross talk expected in the  $n^+$  implant** → **Increase resistivity of  $n^+$  implant**

**DC-LGAD**

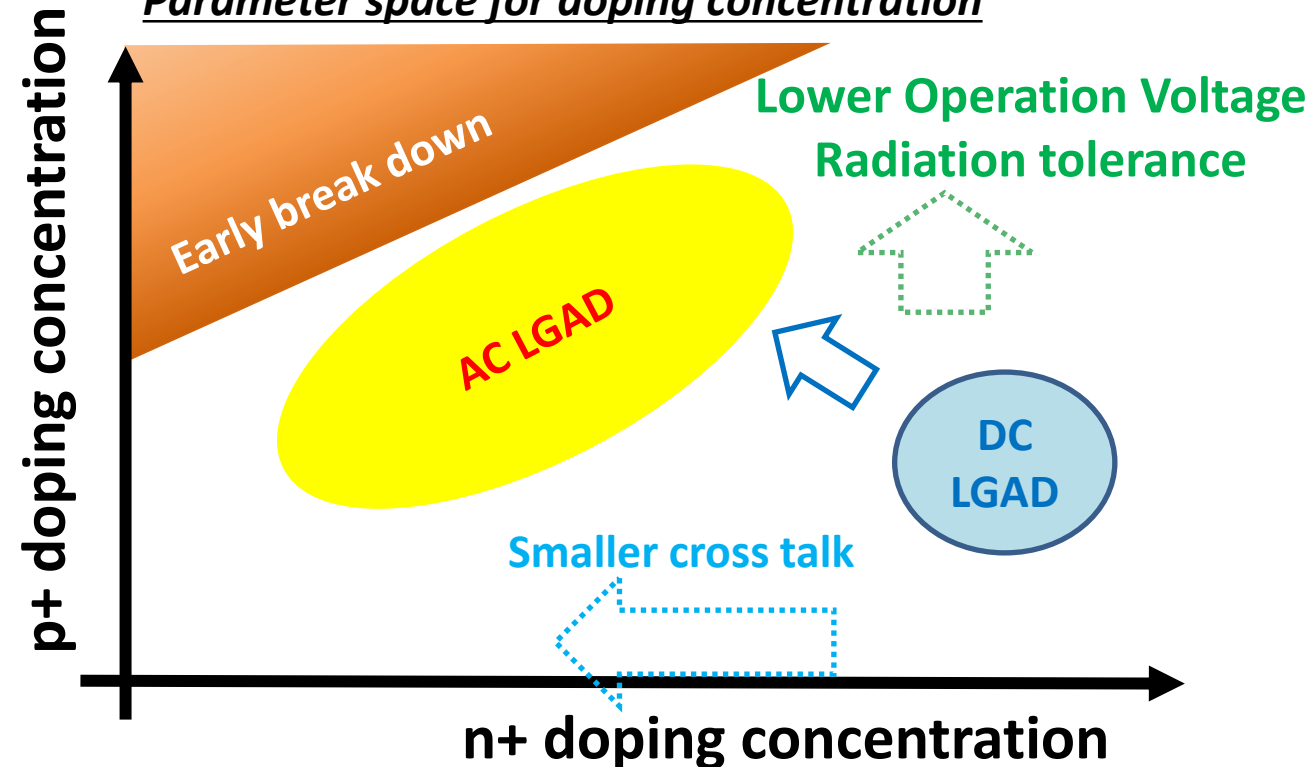


**AC-LGAD**

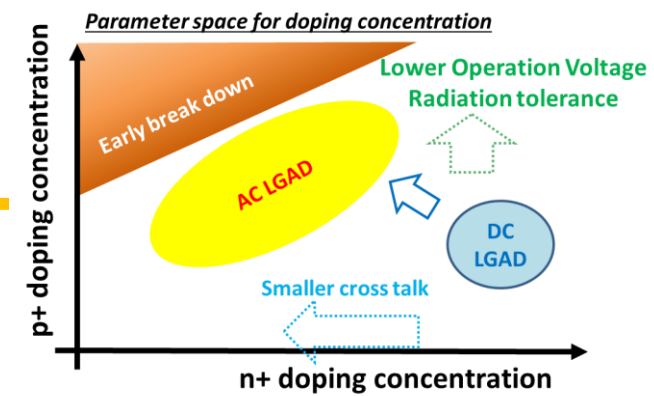
**New**



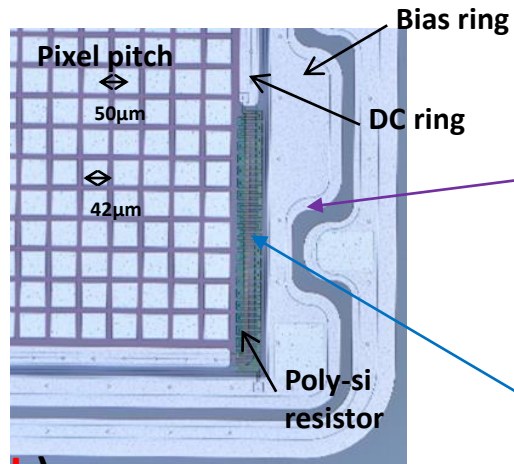
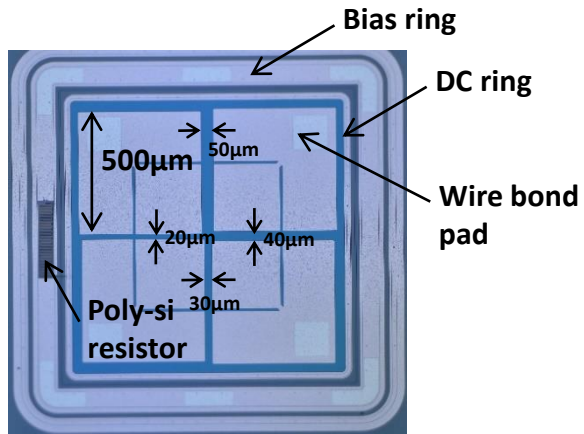
**Parameter space for doping concentration**



# First AC-LGAD by HPK



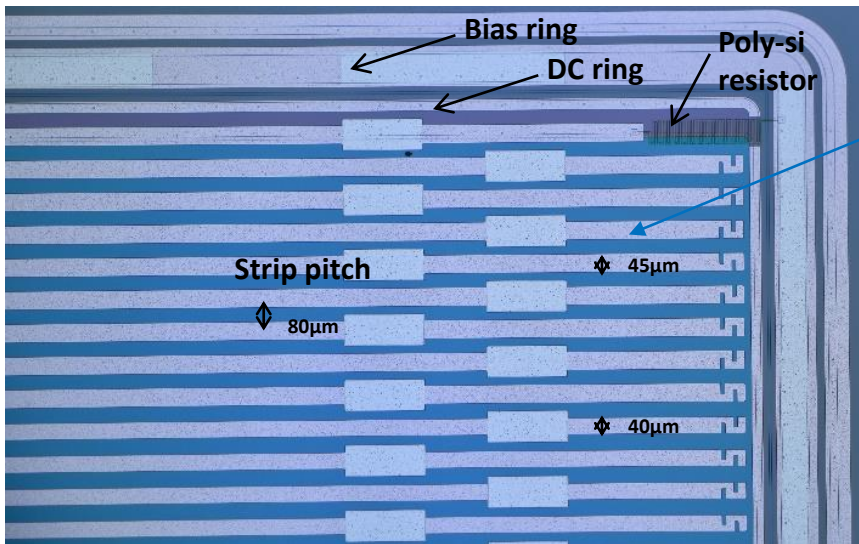
**Pad type sensor (4x 500umx500um)**    **Pixel type sensor (14x14 50umx50um)**



GNDed DC ring via Poly-si  
→ To remove charge in n+

Varied Al size (AC coupling capacitance)  
Pixel : 42/38/34/30 um width/length  
Strip : 45/40/35/30 um width

**Strip type sensor (16x 80um pitch)**



n+ and p+ doping concentration

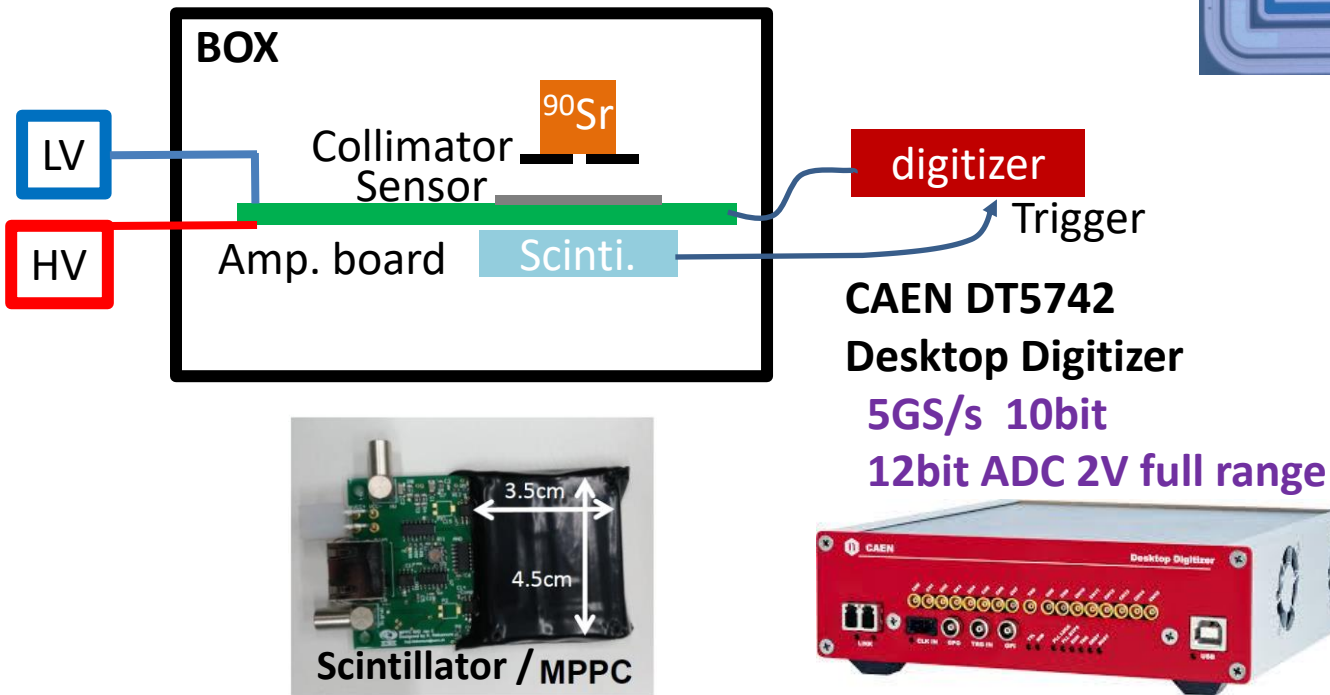
		N+ doping concentration / resistivity		
		C(Ax10 resistivity)	B(Ax3.3 resistivity)	A (~DC-LGAD)
P+ doping concentration	3 (high)		B-3	A-3
	2 (mid)	C-2	B-2	A-2
	1 (low)	C-1	B-1	

Y-axis: p+ doping

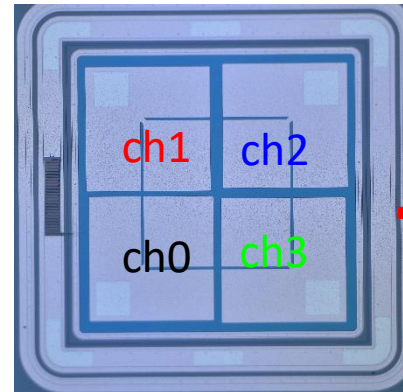
X-axis: n+ doping

# Measurement setup and signal observation

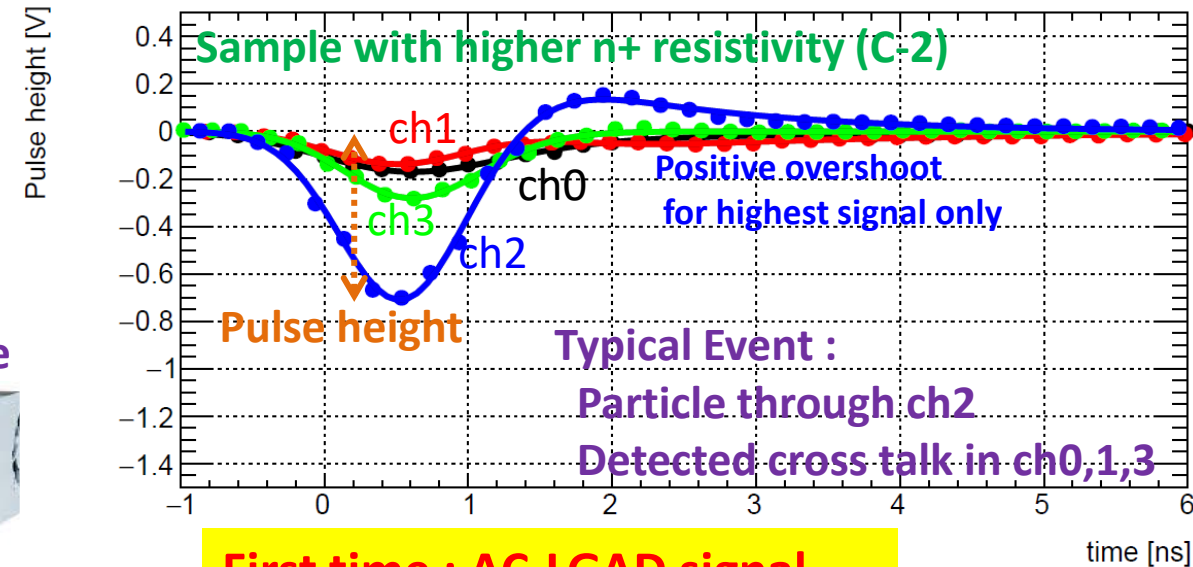
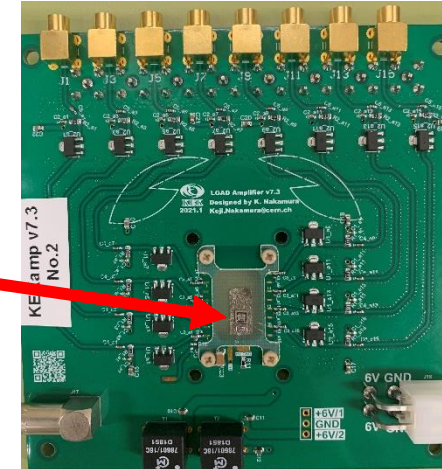
- Lab setup
  - Designed high speed amplifier board.
  - Signal recorded by CAEN DT5742 digitizer
  - $^{90}\text{Sr}$   $\beta$  lay source
  - Triggered by Scintillator (MPPC readout)



Pad Sensor



KEK 16 ch Discrete Amp.



**First time : AC-LGAD signal observed with small crosstalk**

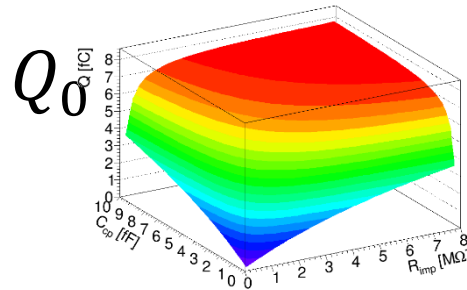


# Equivalent circuit for Signal readout

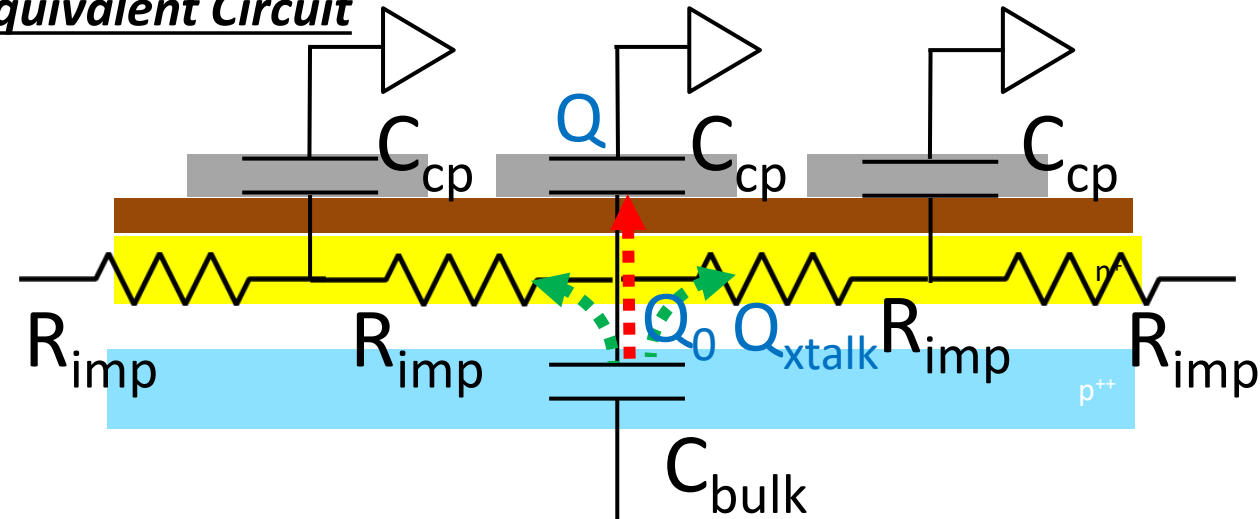
- Crosstalk and Readout charge

Assuming  $Z_{cbulk} \gg Z_{Ccp}$ ...

$$Q = \frac{Z_{R_{imp}}}{Z_{R_{imp}} + Z_{C_{cp}}} Q_0$$



Equivalent Circuit



- Generated charge  $Q_0$
- Readout charge  $Q$

To have larger signal

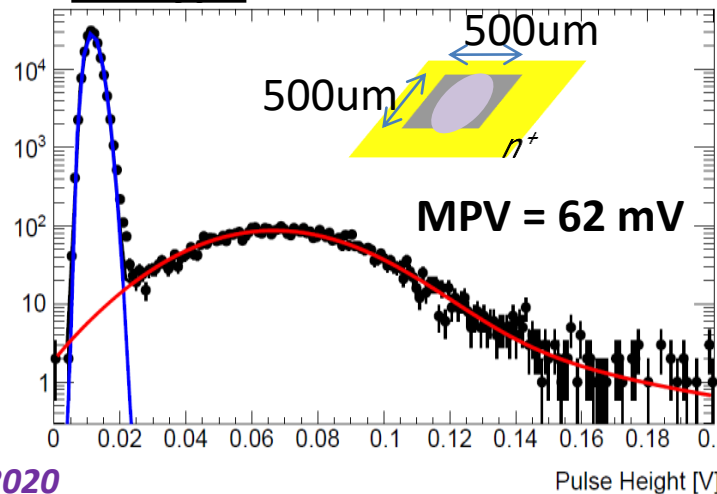
Larger  $C_{cp}$

Larger  $R_{imp}$

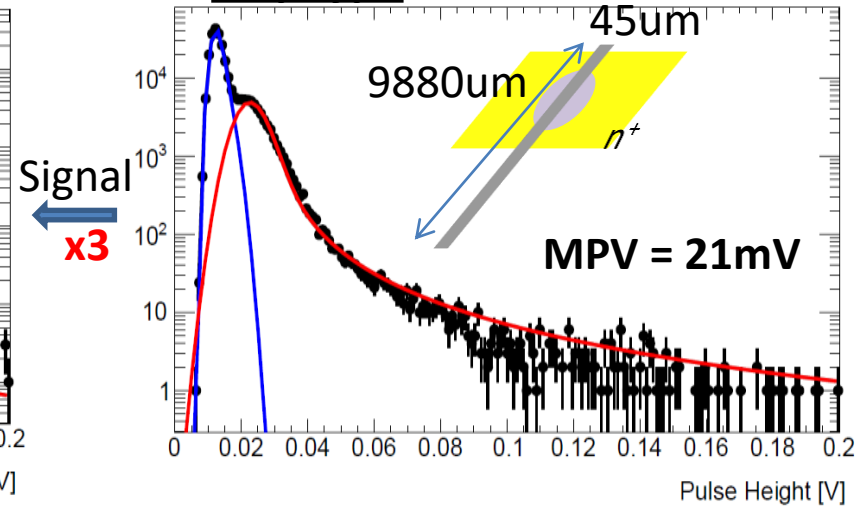
JPS : 12aT3-7 Sayuka Kita (Tsukuba)

See more detail in Last THoU member meeting in 30<sup>th</sup> Nov 2020

Pad type

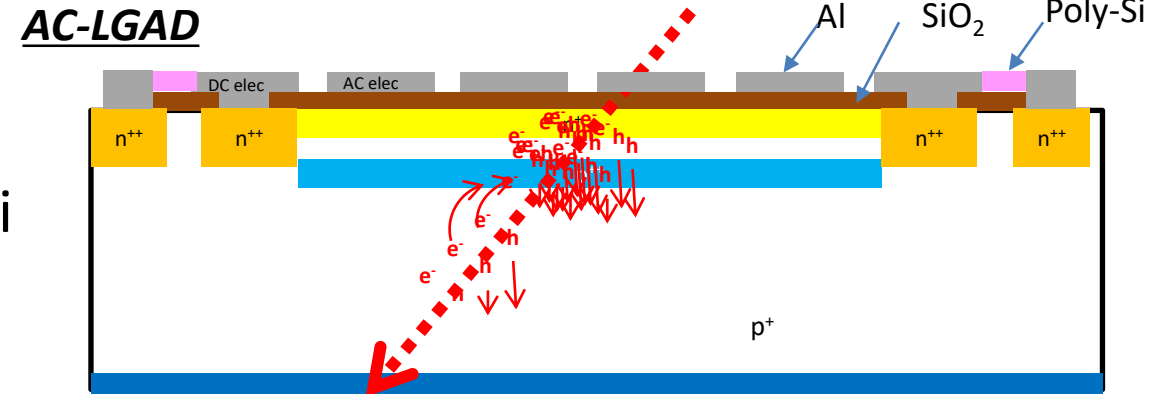


Strip type

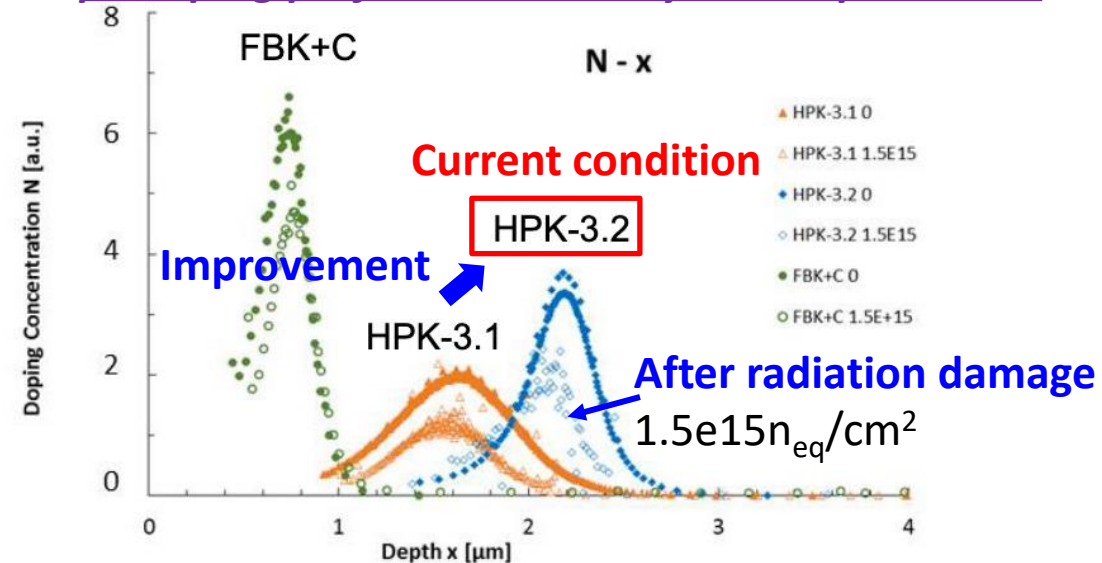


# Radiation Effect in LGAD sensor

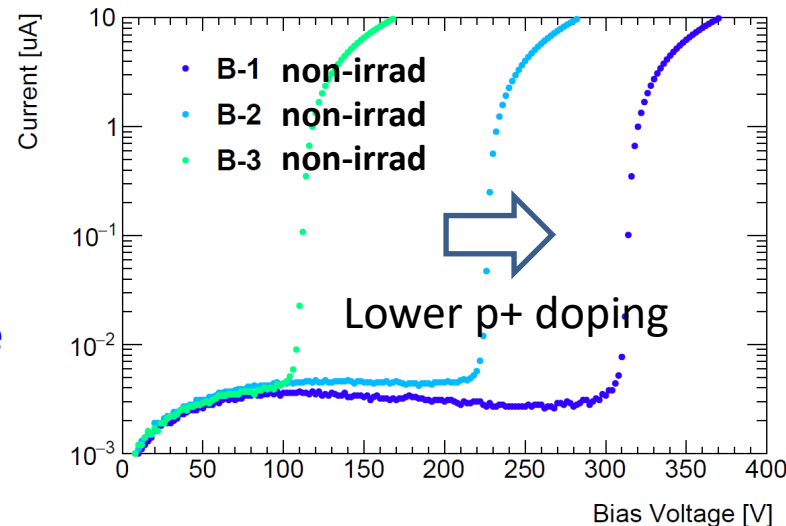
- The same as general  $n^+$ -in- $p$  sensor
  - Bulk damage (NIEL) : Lattice defect.
  - Surface damage(TID) : Positive charge @  $\text{SiO}_2$ -Si
- In addition to this **"Acceptor Removal"**
  - $p^+$  (Boron) acceptor change to doner level



$p^+$  doping profile measured by bulk capacitance



What happened if  $p^+$  dope reduced by acceptor removal?



Reduce  $p^+$  doping concentration



Higher Gain (operation) Voltage



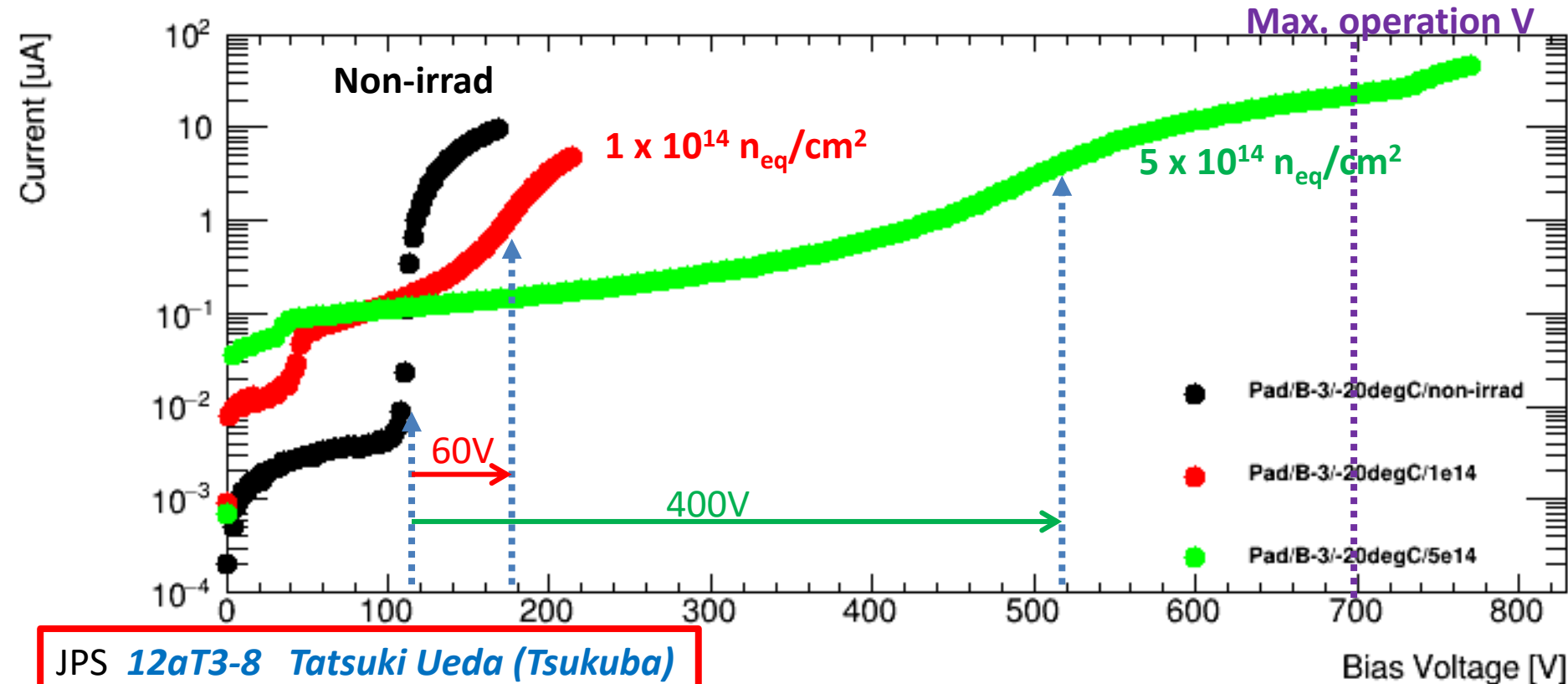
Operation Voltage > Max voltage (~700V)



End of life

# IV performance after irradiation

- Irradiated sensors at CYRIC (Tohoku university) with 70MeV Proton.
- Operation/Gain voltage get higher by irradiation (almost linearly)
  - Current sensor does not work after  $1 \times 10^{15} n_{eq}/cm^2$  fluence or more.



Signal Size	
Fluence	Signal MPV
Non-irrad	35±2 mV
$1 \times 10^{14} n_{eq}/cm^2$	39±1 mV
$5 \times 10^{14} n_{eq}/cm^2$	30±2 mV

$5 \times 10^{14} n_{eq}/cm^2$  may have slight decrease of signal (But keep at least ~75%)

JPS 12aT3-8 Tatsuki Ueda (Tsukuba)

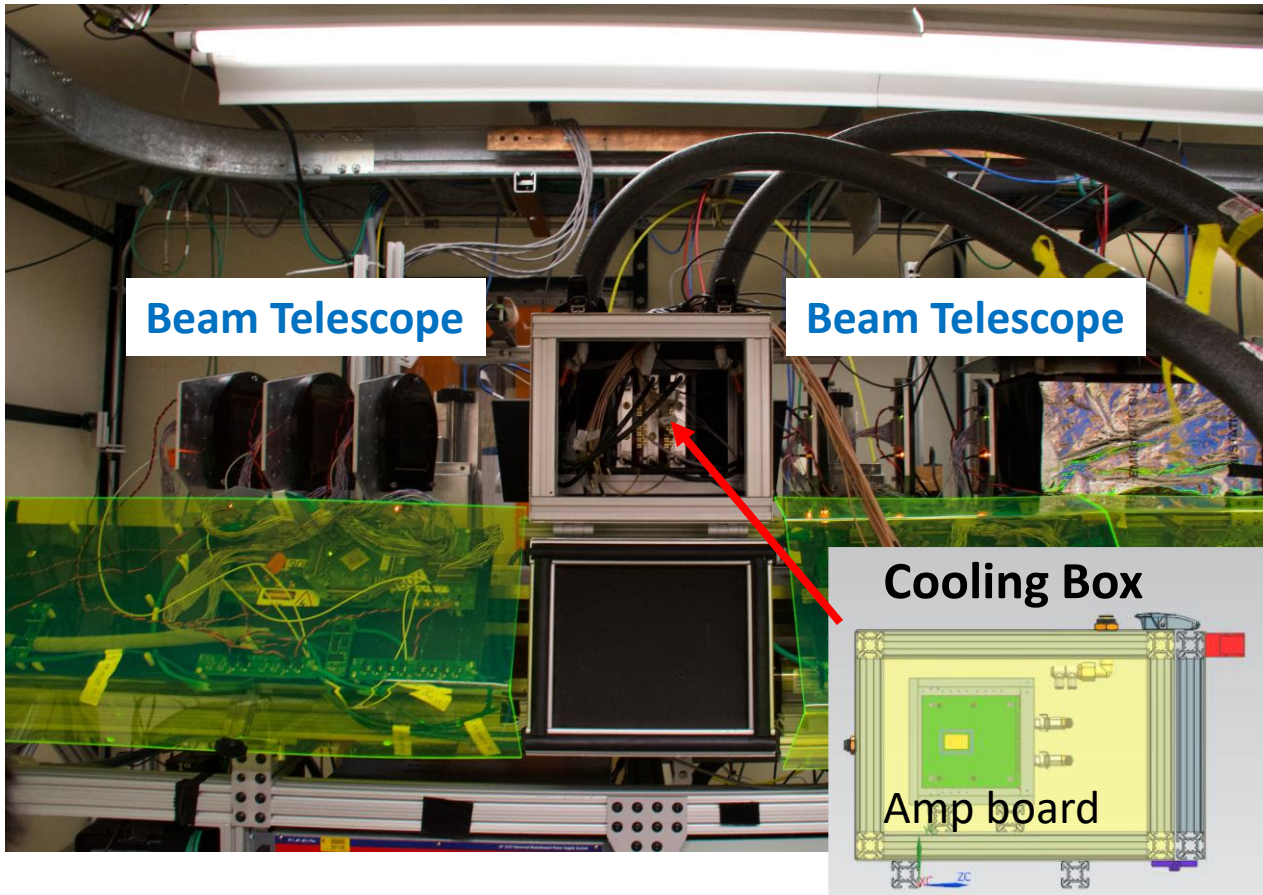
# Test beam in Feb 2021 @ Fermilab

*Not participate in person due to COVID-19*

## Fermilab Test Beam Facility (FTBF)

120GeV proton beam

Strip Detector based Telescope :  $\sim 15\mu\text{m}$  pointing resolution



## Readout by Oscilloscope

LeCroy  
WR8208HD scope  
12bit, 10GSa/s, 2GHz  
8 channel



## Timing reference Detector

PHOTEK  
MCP photomultipliers (PMT140)  
450ps FWHM with  $5e3$  Gain

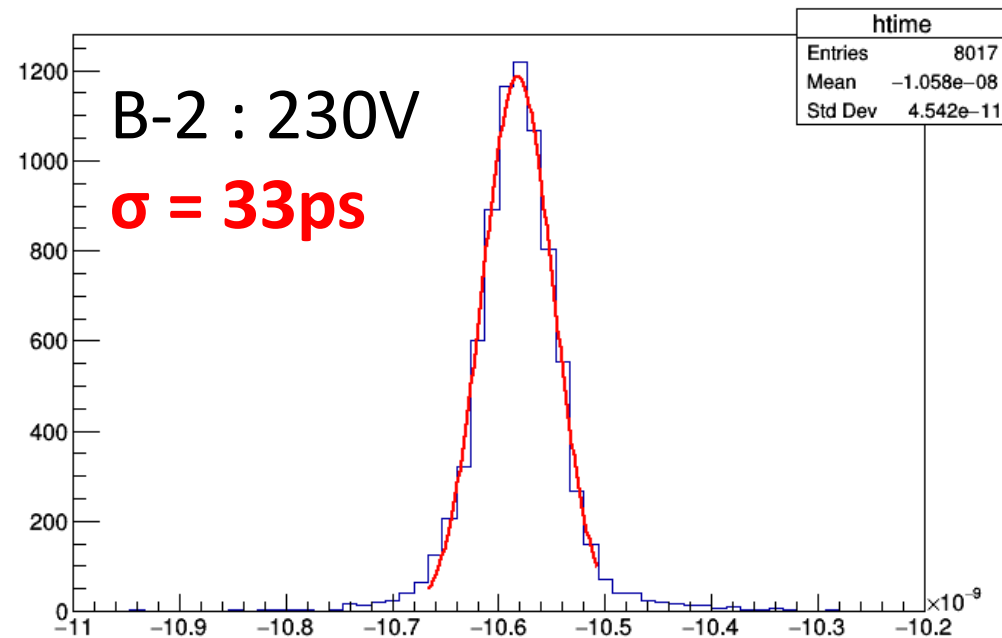
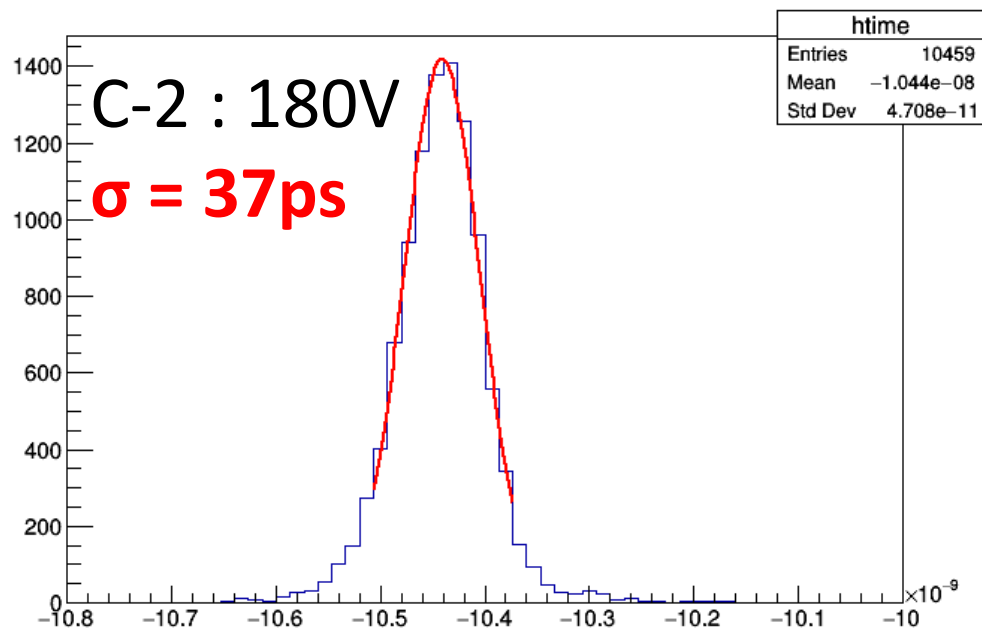
**$\sim 5\text{ps}$  timing resolution**  
**(SPEC: Multi-photon jitter below 10 ps)**



# Time resolution measurement @ testbeam

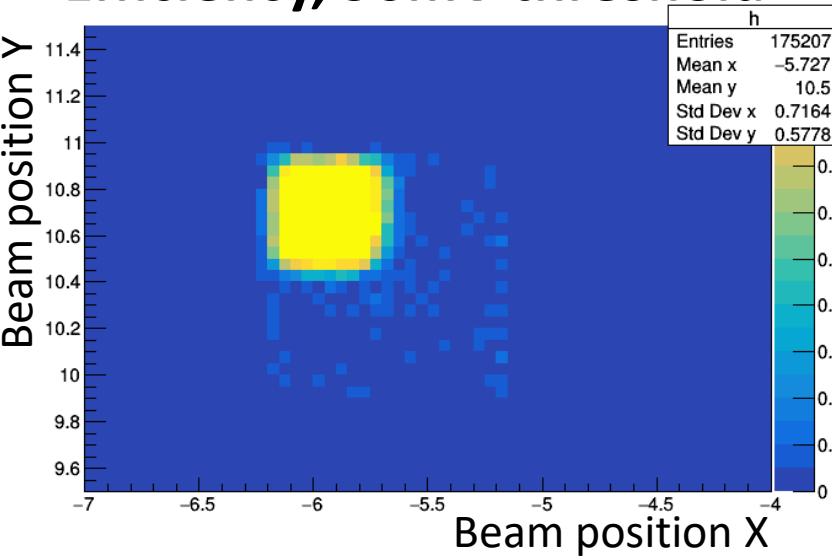
- Used PHOTEK : MCP PMT140 as a timing reference detector
  - Including 5ps PMT140 time resolution (<1% effect)

Very fresh results : Obtained 30-40ps time resolution for a couple of types of sensors

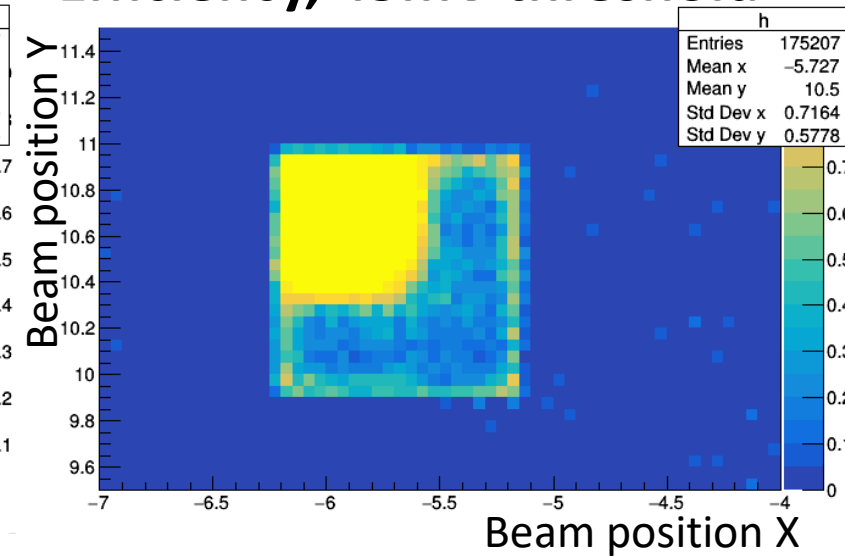


# Efficiency and signal sharing @ testbeam

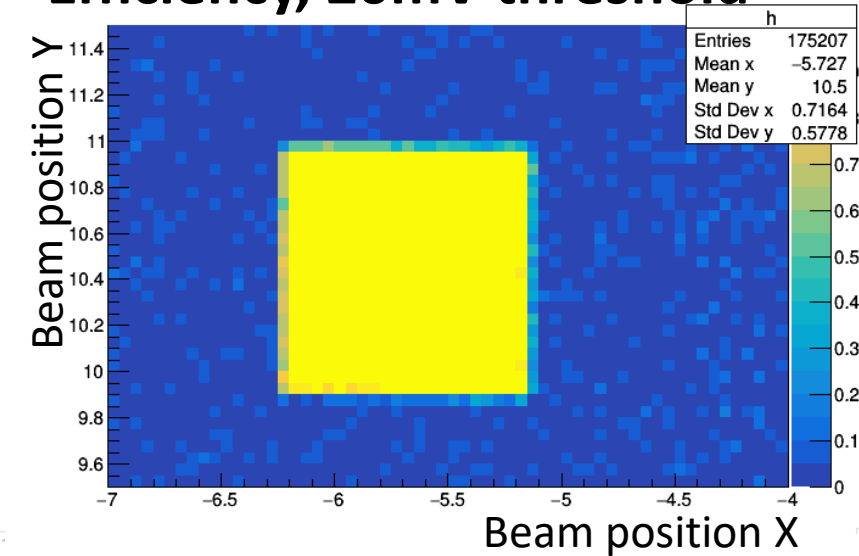
Efficiency, 90mV threshold



Efficiency, 45mV threshold



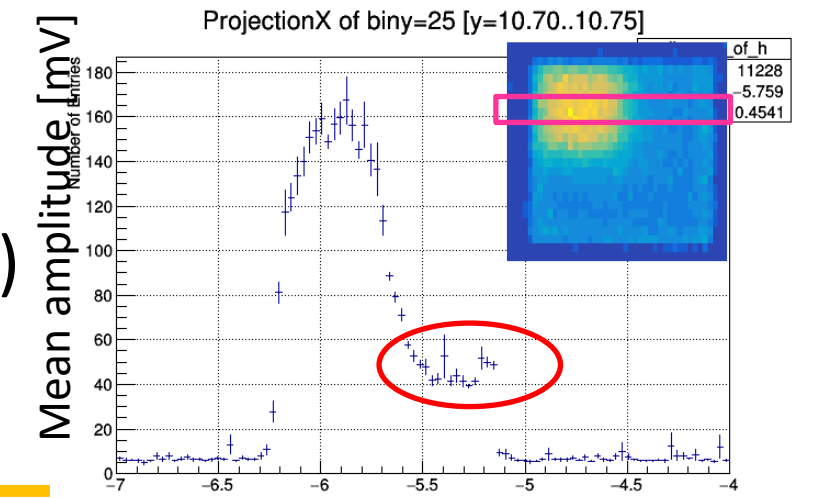
Efficiency, 20mV threshold



- Efficiency measurement for the top left pad.
  - Close to 100% efficiency @ 90mV threshold
  - ~40mV crosstalk observed. (consistent to lab meas.)



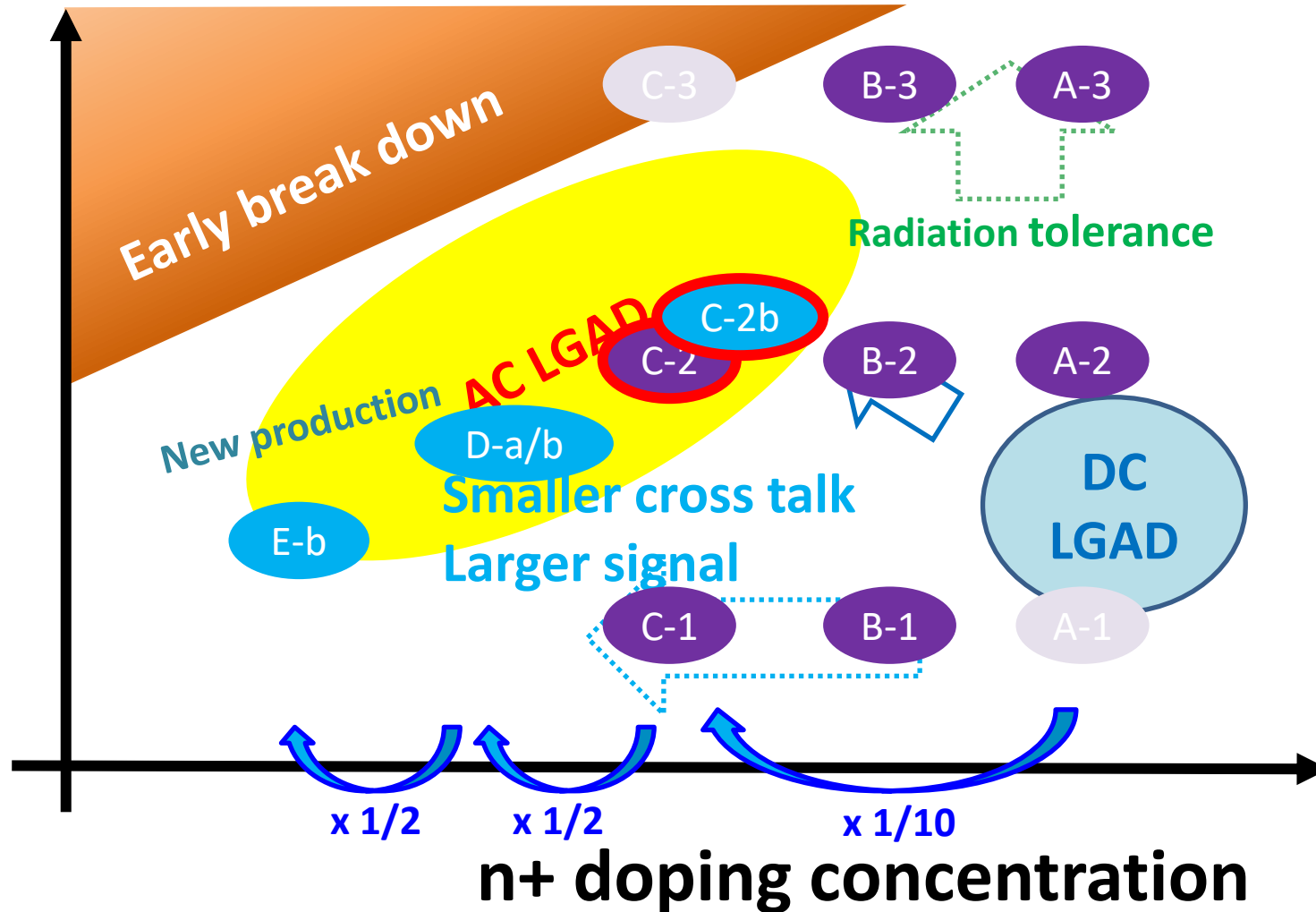
Need more study for the reason of flat crosstalk. (inter elec. Cap?)



# New samples (4 types of sensors)

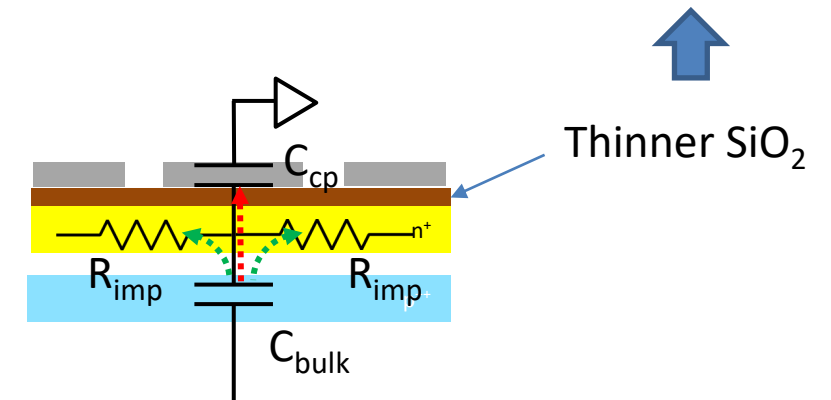
Parameter space for doping concentration

p+ doping concentration

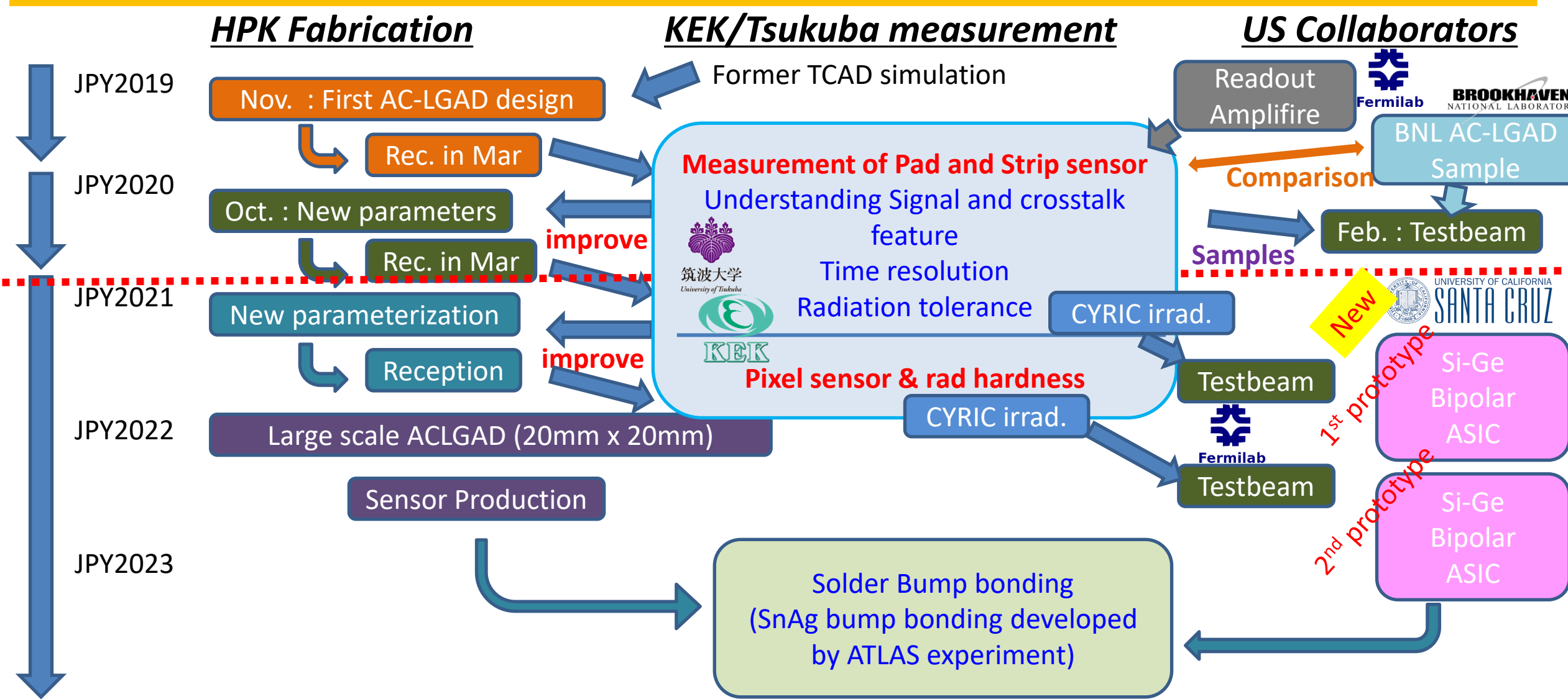


- Existing Samples
- New Samples (26<sup>th</sup> Mar)

		Coupling capacitance	
		Nominal x 1	Nominal x 1.5
$n^+$ resistivity	Ax10	C-2	C-2-b
	Ax20	D-a	D-b
	Ax40		E-b



# Summary and plan

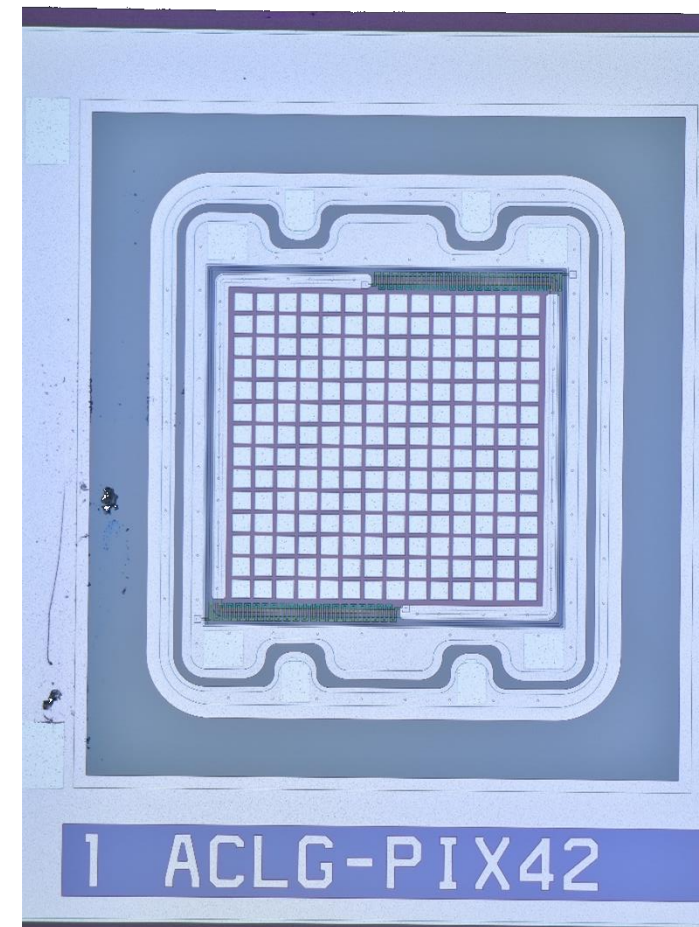
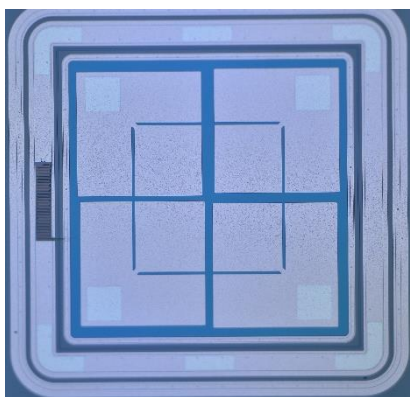
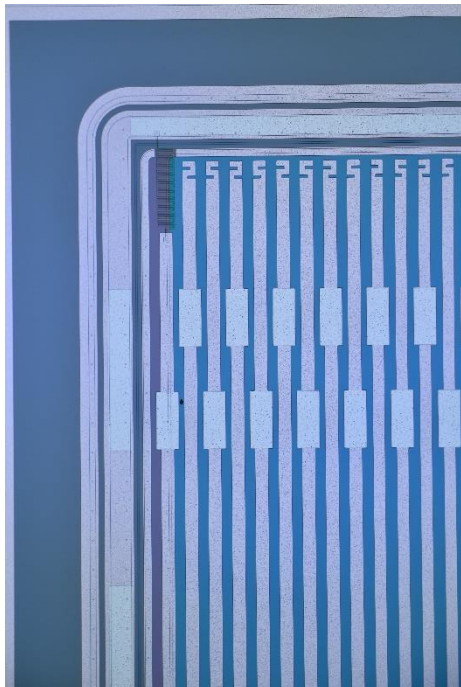
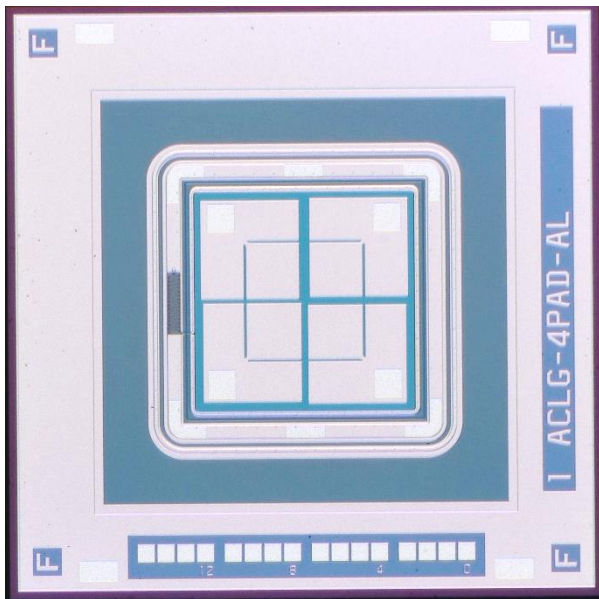




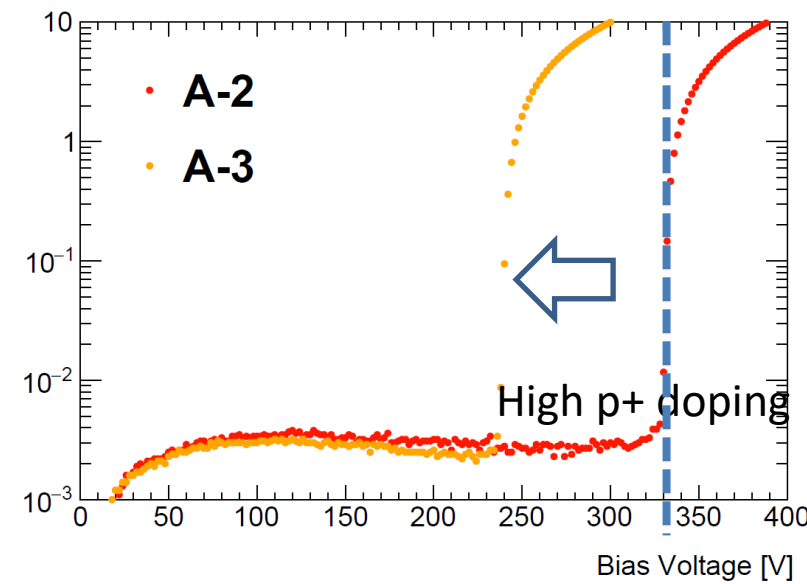
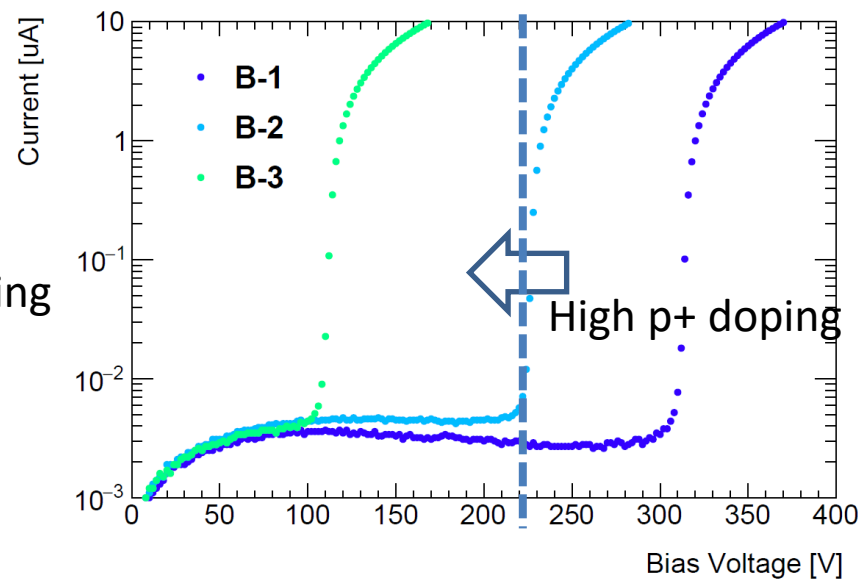
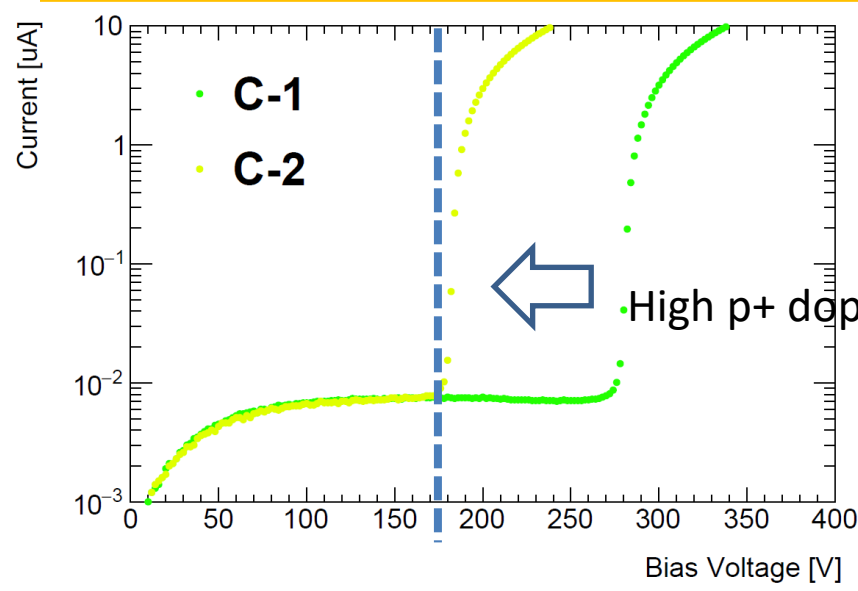
# backup

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# Photo



# Leakage current vs Bias voltage



Break down (gain) voltage get lower

- Higher P+ dope
- Lower N+ dope

→ Radiation tolerance

**C-2 type :**

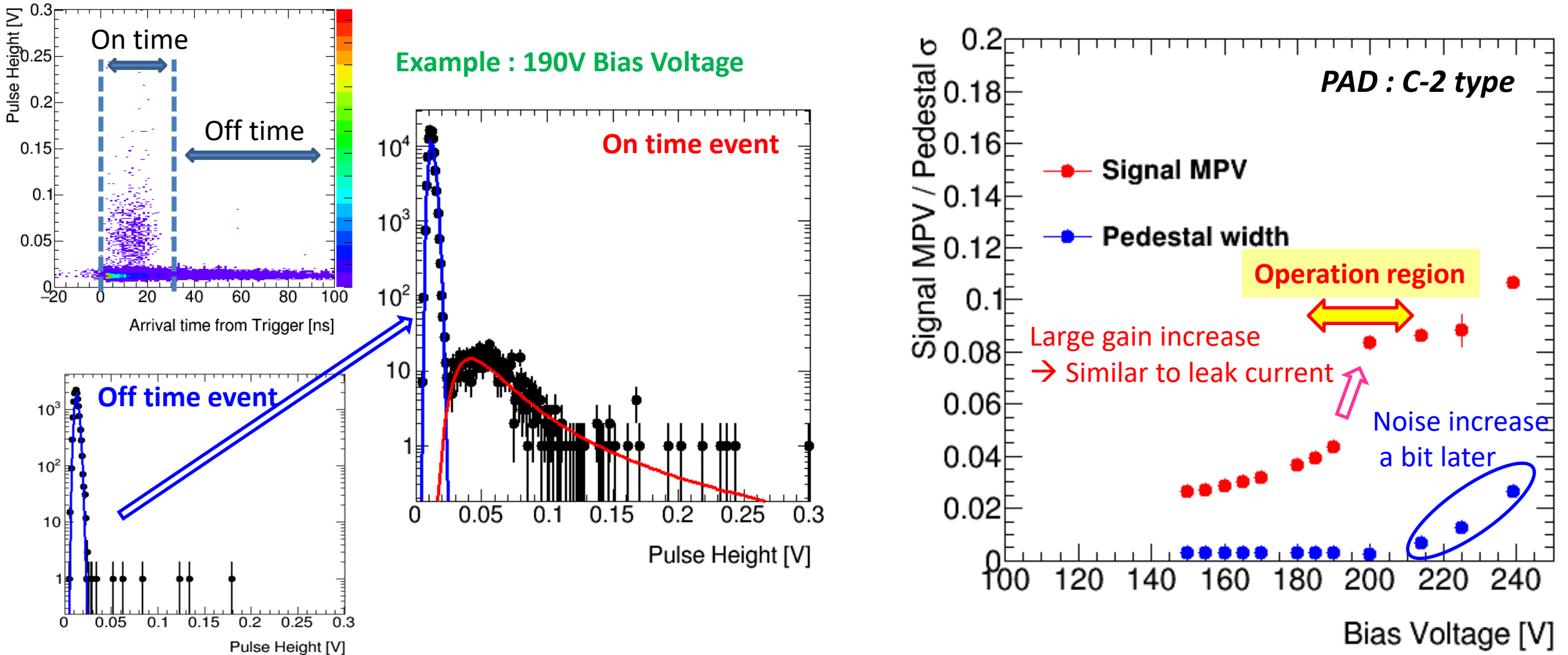
- Lower operational voltage
- Smaller crosstalk

## Variation of p+ and n+ doping concentration

		N+ doping concentration / resistivity		
		C(Ax10 resistivity)	B(Ax3.3 resistivity)	A (~DC-LGAD)
p+ doping concentration	3 (high)		B-3	A-3
	2 (mid)	C-2	B-2	A-2
	1 (low)	C-1	B-1	

# Pulse Height and Bias Voltage dependence

Pedestal distribution is evaluated from off timing region



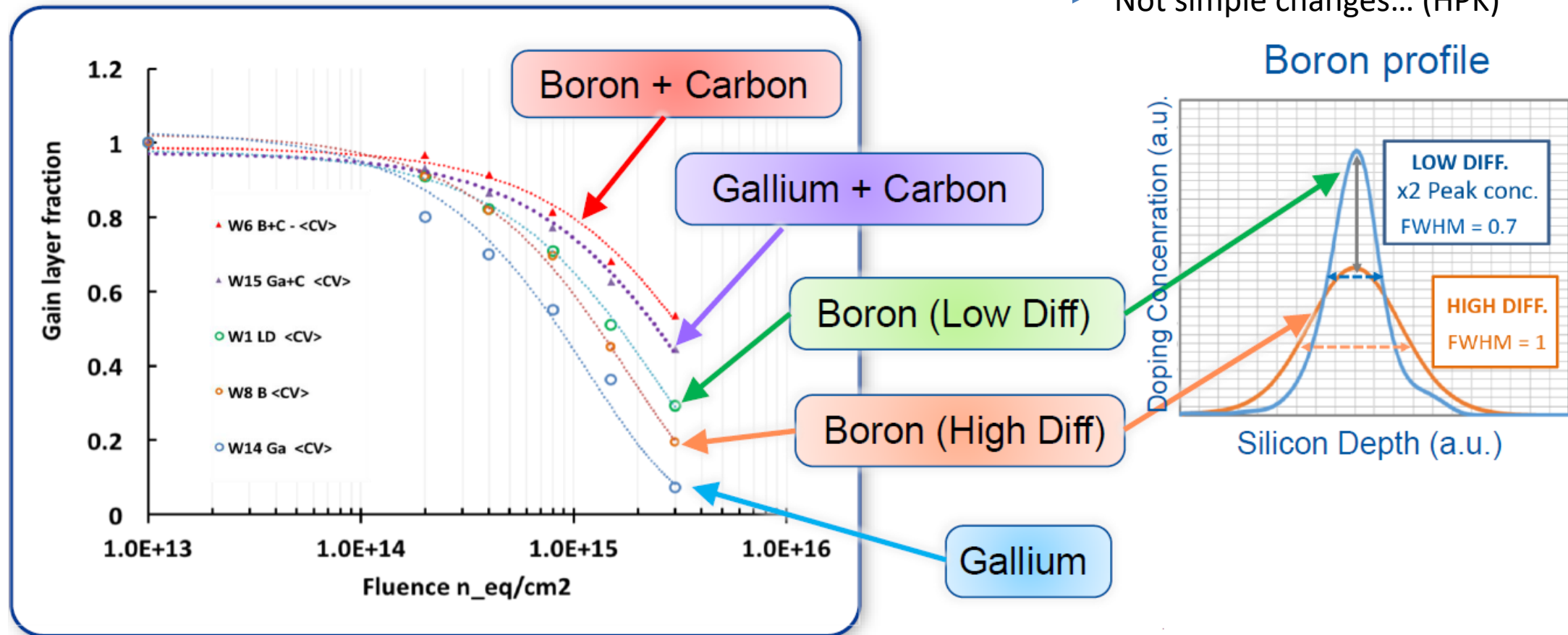
# How to reduce “Acceptor Removal” effect?

- Study by FBK LGAD sensors.

Two way

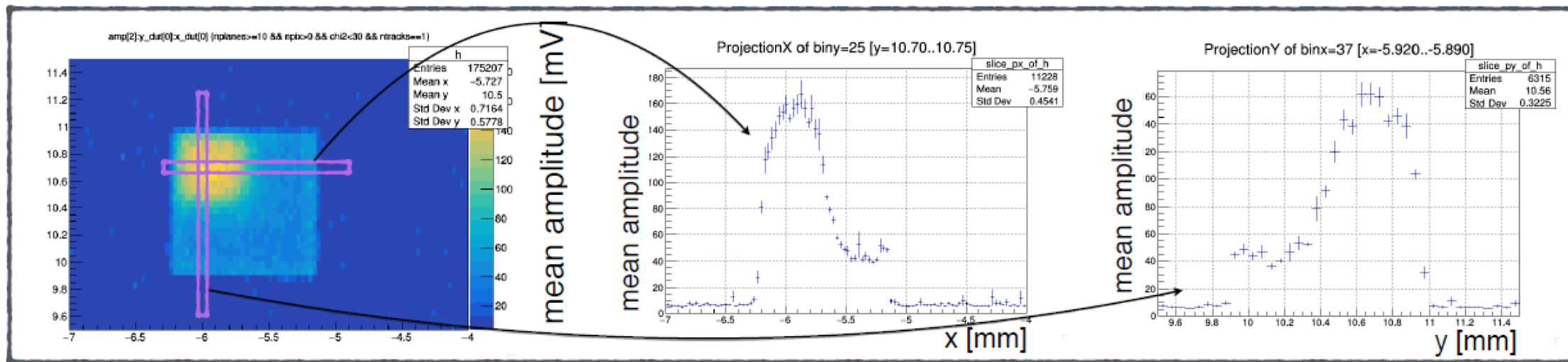
1. Lower diffusion of Boron doping profile
2. Adding carbon (or Gallium) to  $p^+$  layer

→ Not simple changes... (HPK)

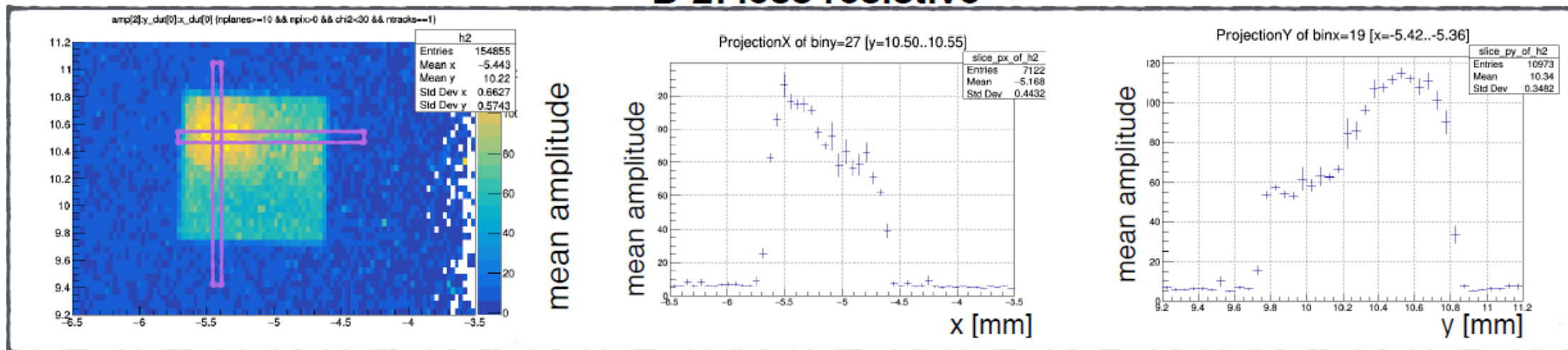


# Position dependent mean amplitude

## C-2: more resistive



## B-2: less resistive



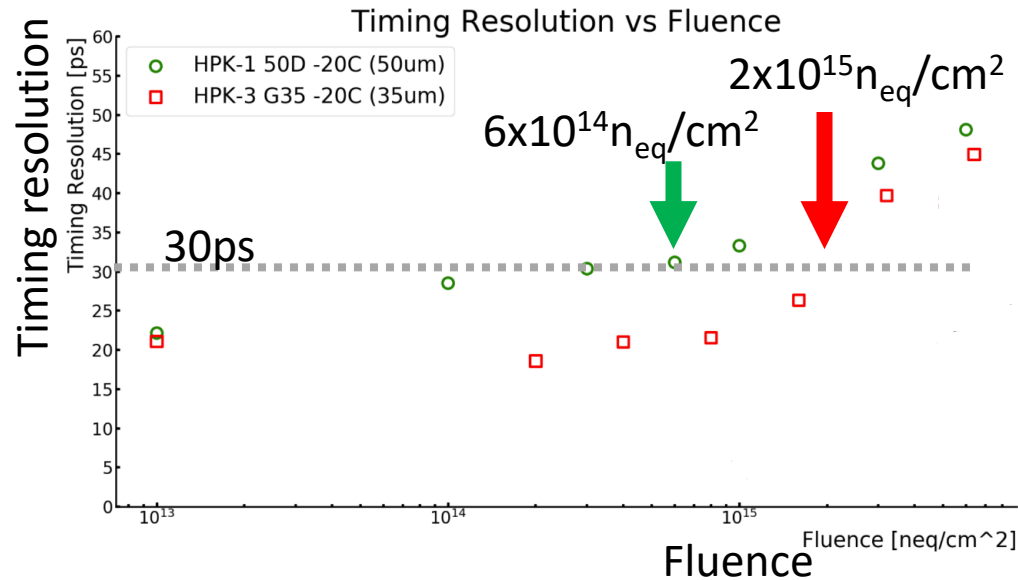
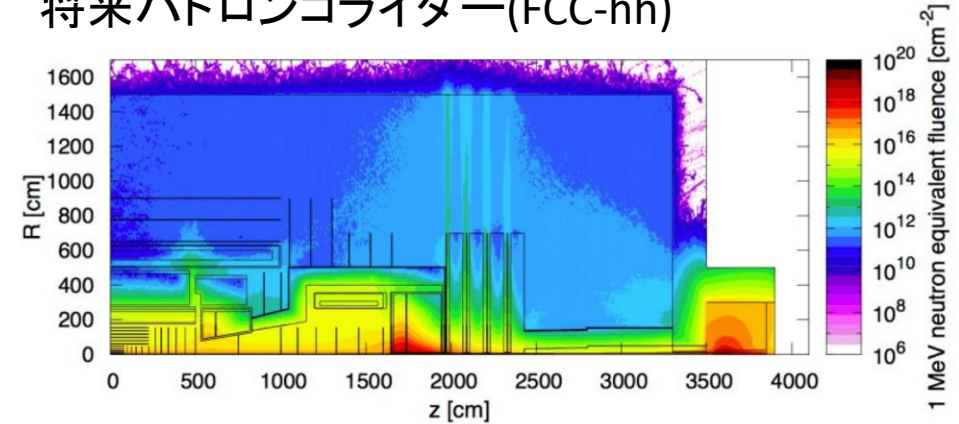
# Radiation Tolerance

- Radiation Tolerance**

Current :  $0.6-2 \times 10^{15} n_{eq}/cm^2$

Goal :  $1 \times 10^{16} n_{eq}/cm^2$

将来ハドロンコライダー(FCC-hh)



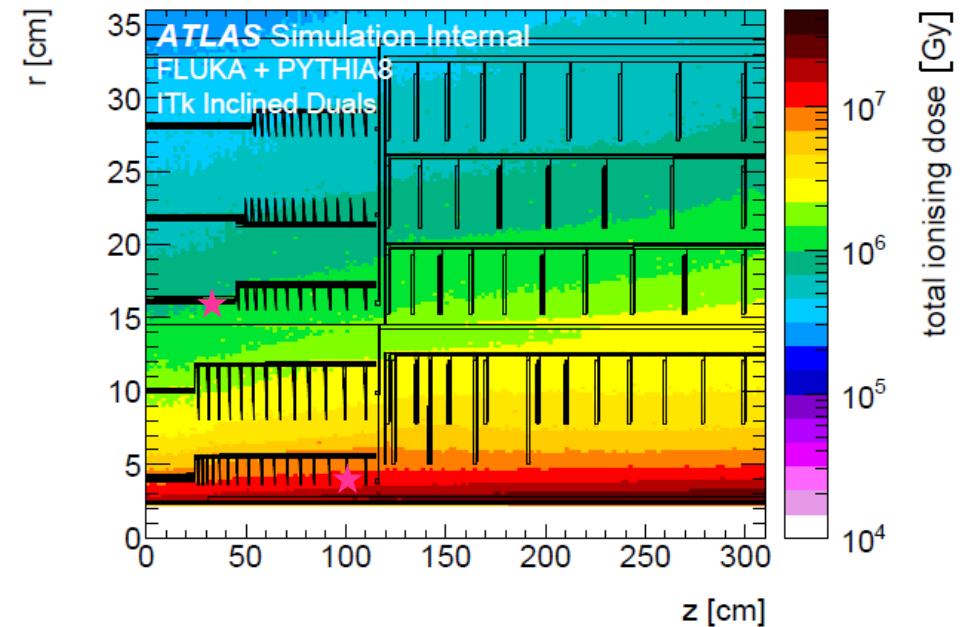
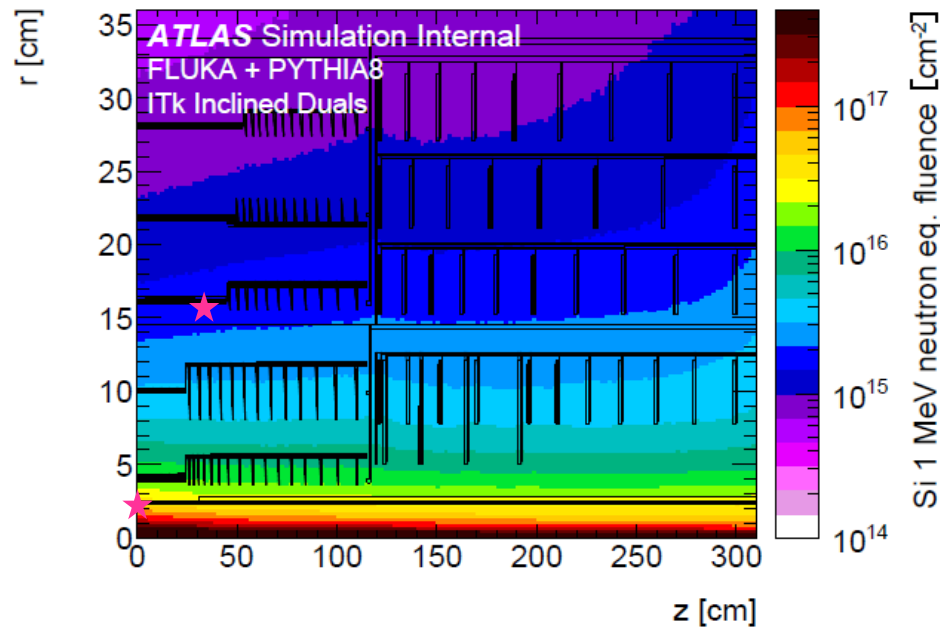
Idea for improvement?

Thinner active thickness and optimized p+ doping

# Radiation environment

- Expected radiation level for  $4000\text{fb}^{-1}$ 
  - Non Ionizing Energy Loss (NIEL):
    - 3<sup>rd</sup> layer:  $2.8 \times 10^{15} \text{ n}_{\text{eq}}/\text{cm}^2$  1<sup>st</sup> layer :  $2.6 \times 10^{16} \text{ neq}/\text{cm}^2$
  - Total Ionizing Dose (TID) :
    - 3<sup>rd</sup> layer : 1.6MGy 1<sup>st</sup> layer : 19.8MGy

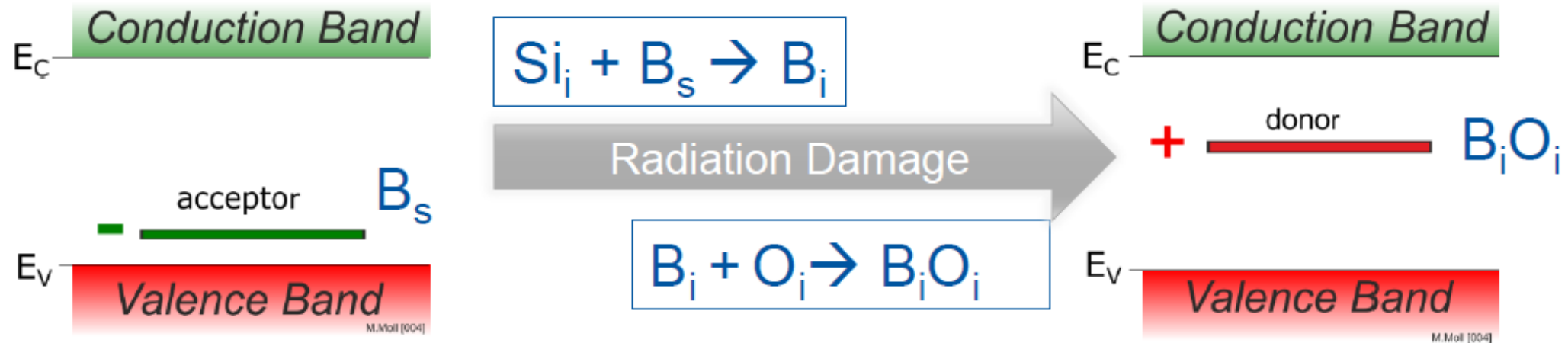
Could replace detector  
at the middle of runs.

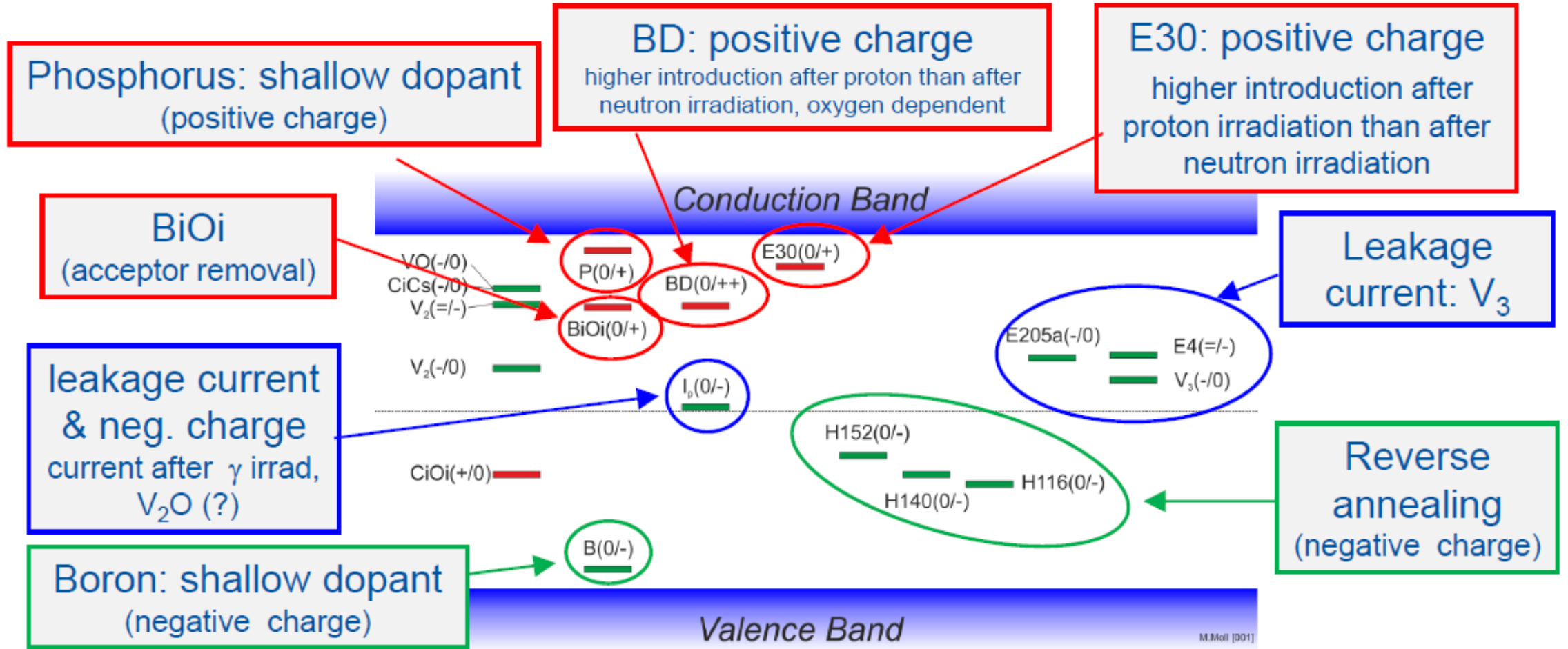




# Acceptor removal

- Most typical radiation induced reaction:

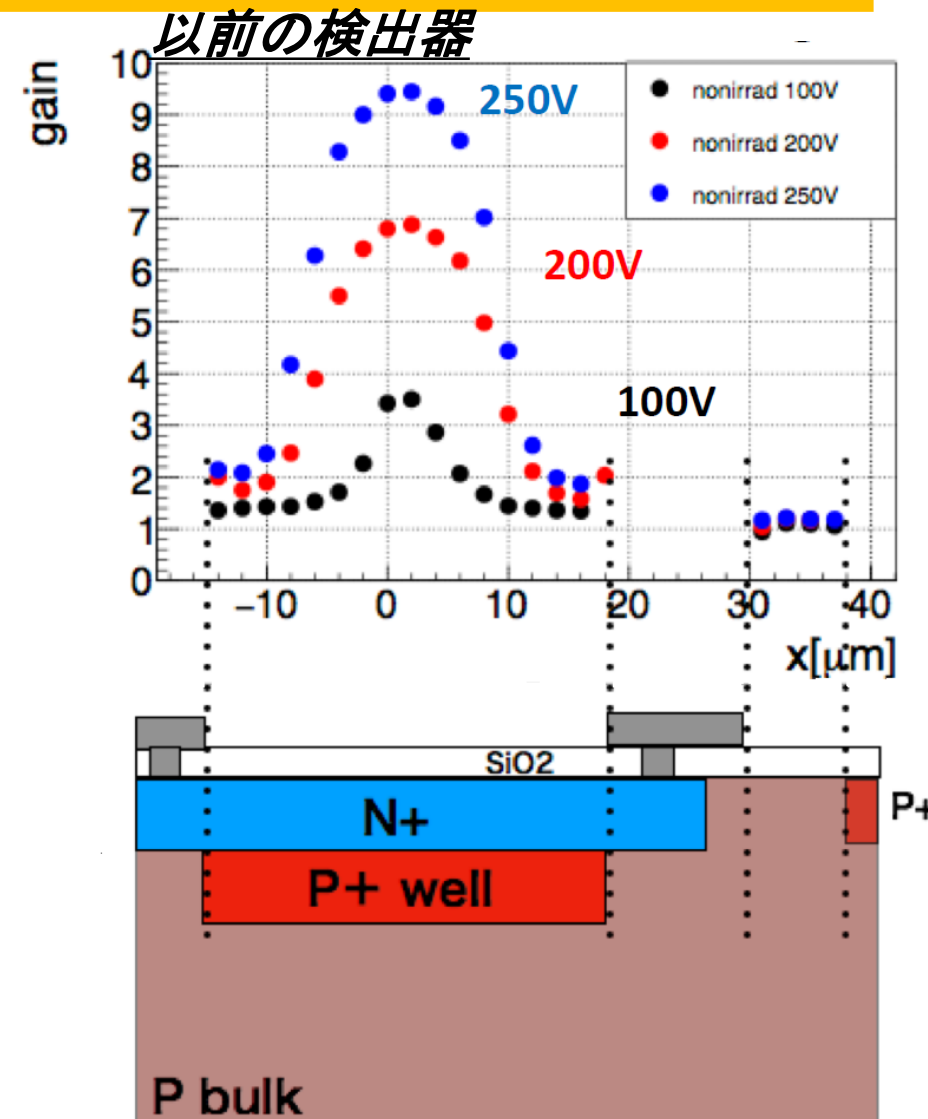
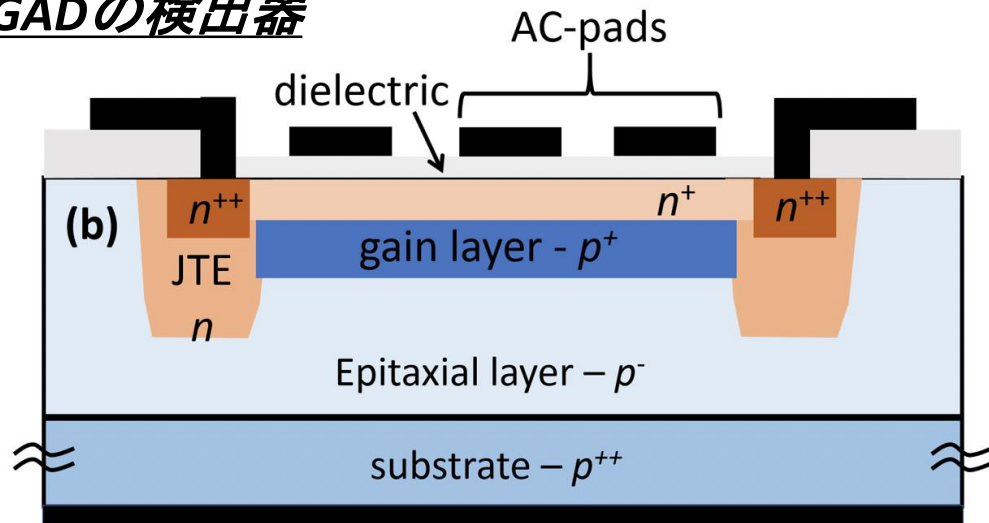




# 新型LGAD検出器(AC-LGAD)

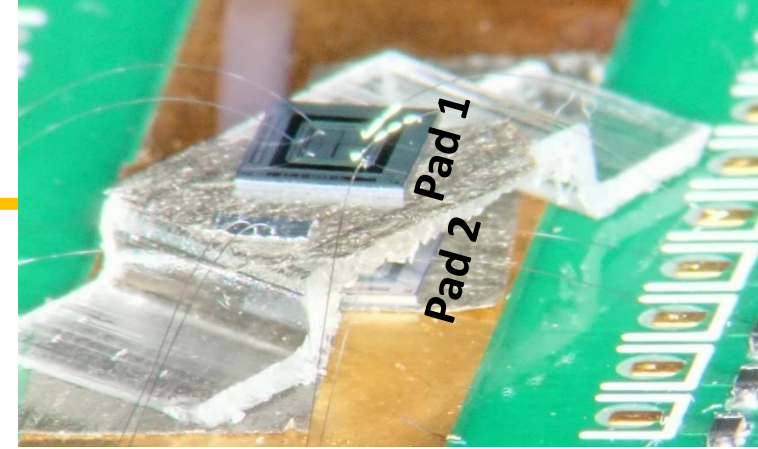
- 電極の細密化が課題
  - 以前の検出器は80 $\mu\text{m}$ ピッチのストリップ型で有感領域が20 $\mu\text{m}$ 程度
  - 各ストリップごとで増幅層が独立(大きくすると電場が不安定)
  - **AC-LGAD** : 一つの増幅層で、AC電極を配置 $\rightarrow$ n+のドーピング量を減らして抵抗値を高くしてクロストークを減らす。
  - $\rightarrow$  n+とp+のドーピング量で増幅率が決まるので最適化が必要

AC-LGADの検出器



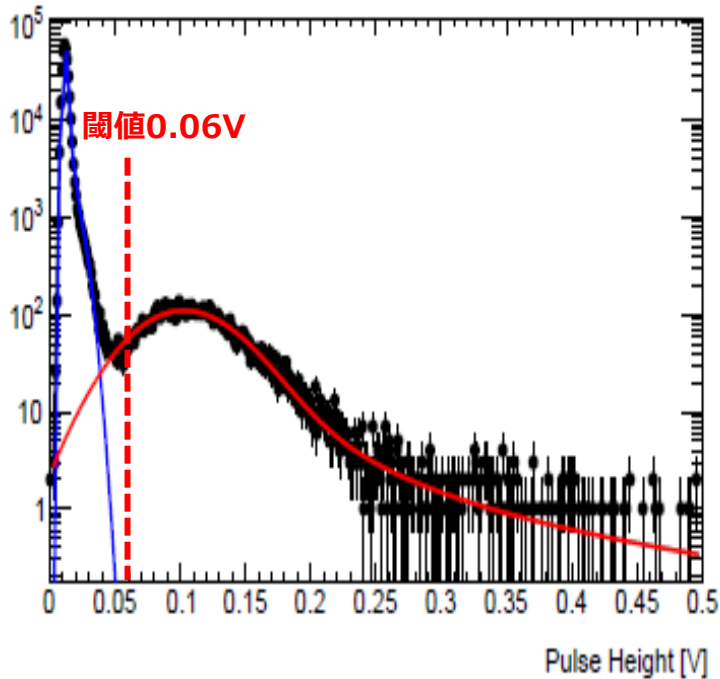
# 時間分解能の測定

- 二枚の同種のセンサーを上下に配置
  - 時間差分布の標準偏差:  $\sigma(T_1-T_2)=\sqrt{(\sigma_1)^2+(\sigma_2)^2}$
  - 同種のセンサーなので:  $\sigma_t = \sigma(T_1-T_2)/\sqrt{2}$



*Timing resolution with certain threshold*

Pulse Height Distribution



Time difference of pad 1 and 2

